

Development of High Speed Sampling ASIC Analog Memory Cell for Imaging Atmospheric Cherenkov Telescope

IMPRS workshop
2011/5/2 in München
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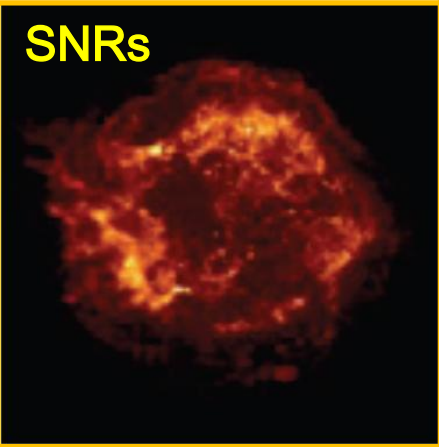
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 - AMC design detail
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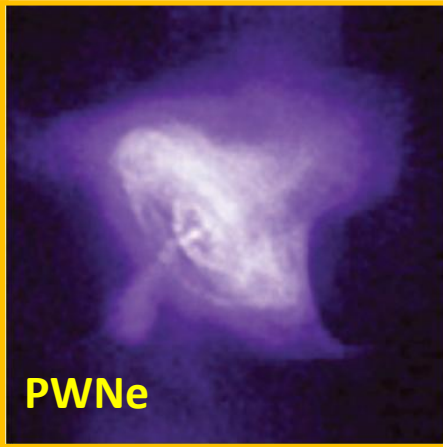
Very high energy gamma ray astronomy

- A hundred of TeV gamma ray sources have been detected by Imaging Atmospheric Cherenkov Telescopes
for example, PWNe, GC /, AGN , star burst galaxies and UnIDs

SNRs



PWNe



GRB

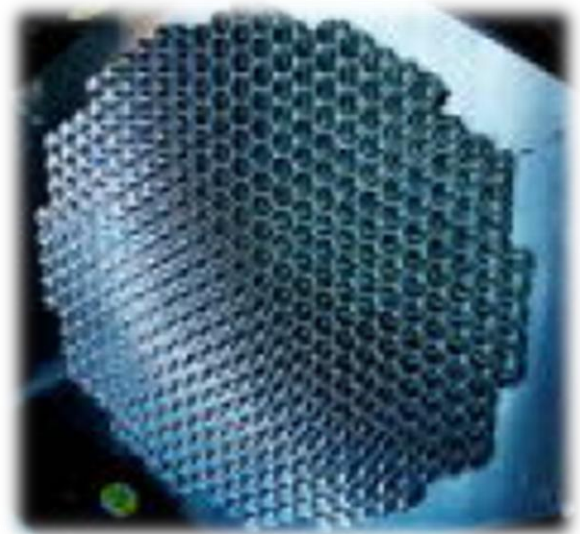
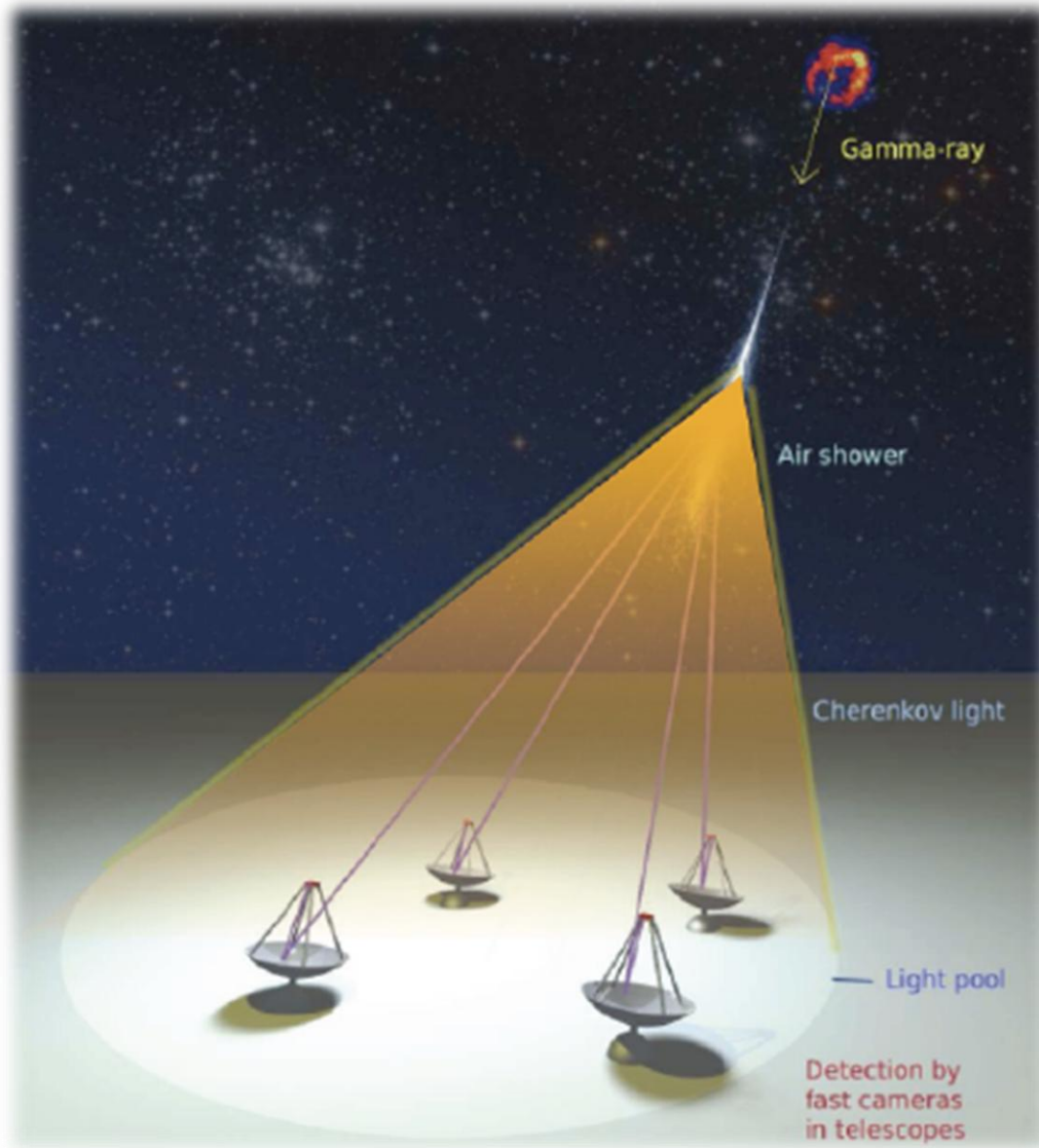


AGN

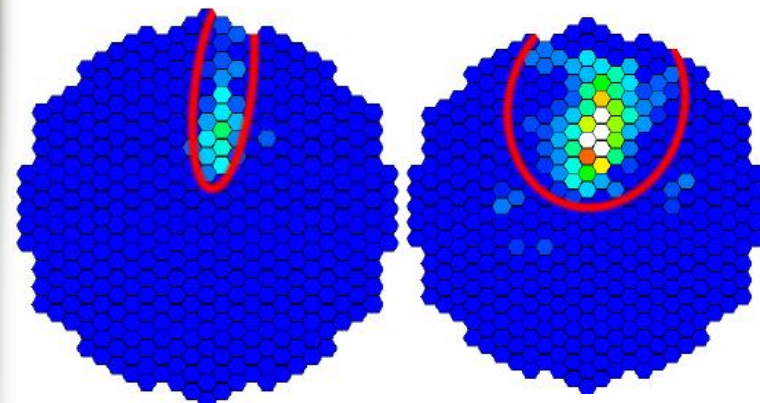


- These lead to understanding radiation mechanisms
- In particular, low energy ($<50\text{GeV}$) observations enable us to study the early universe

IACT observation system



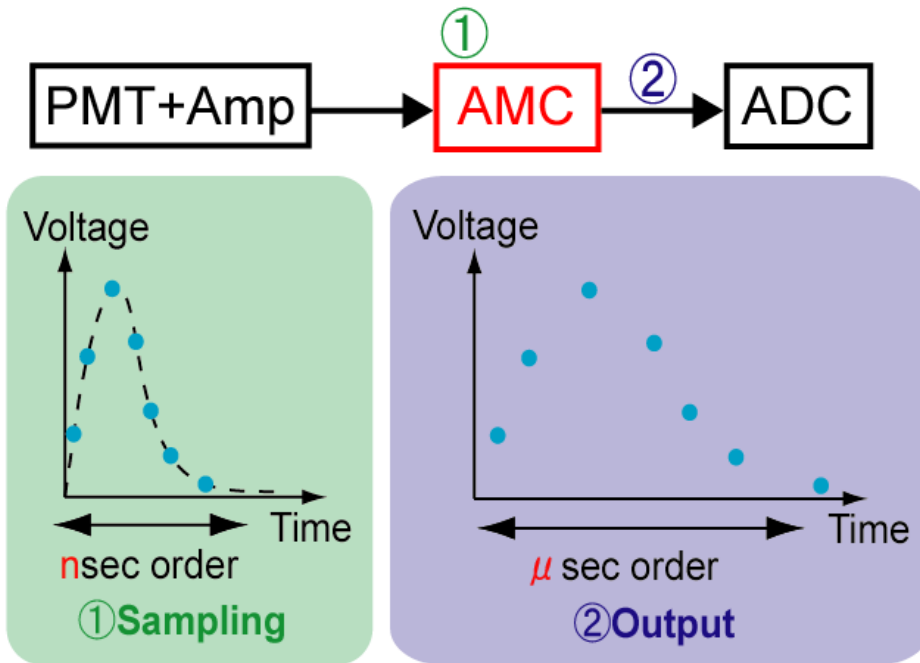
PMT camera



Event of gamma ray

Event of hadron

Analog Memory Cell(AMC)

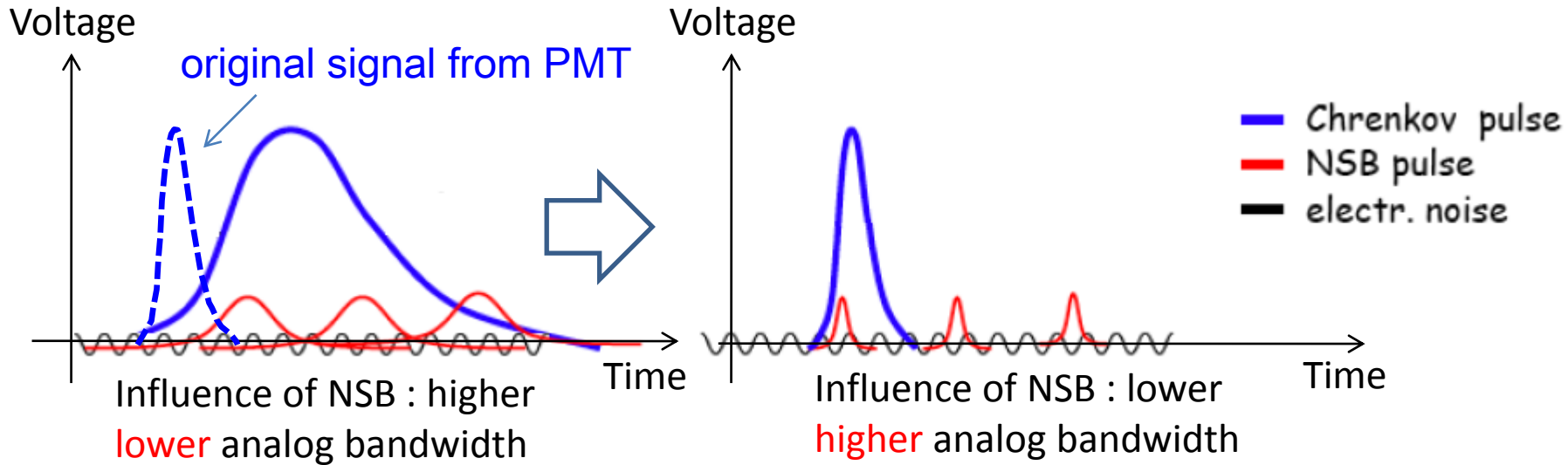


- ① Samples wave form with fast speed 1GHz and high precision over 10bits
- ② Reads out sampled data with slowly <50MHz
 - Slower ADC can digitize the readout data

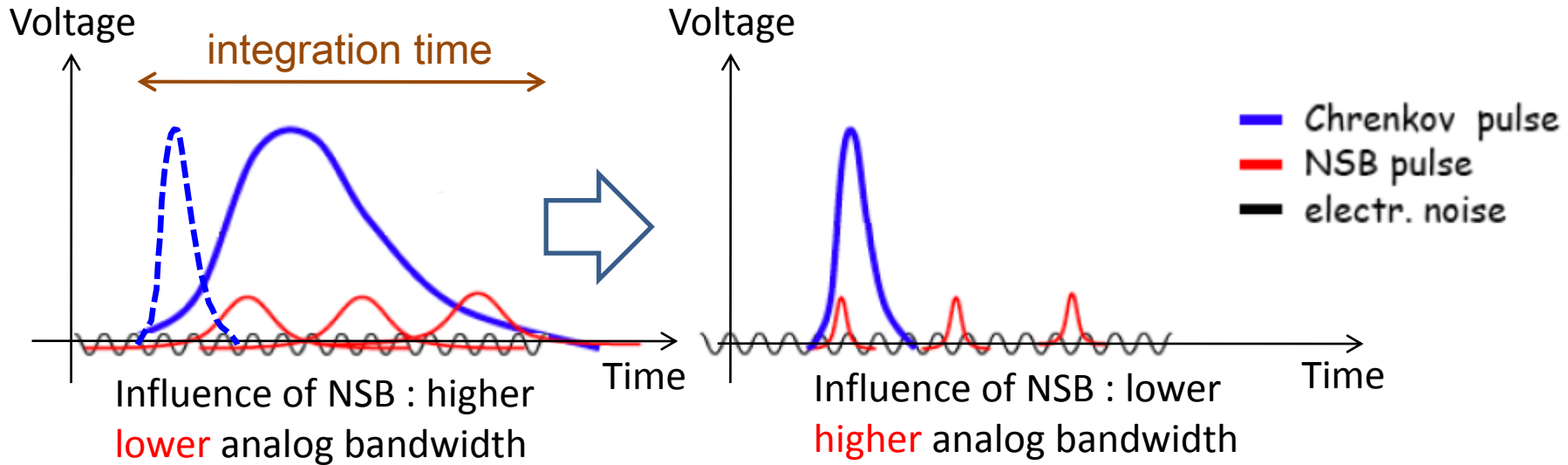
Why did we select not FADC but AMC system?

- **better precision(>10bits)**
- **lower power consumption** (order of mW)
(cf: power consumption of FADC is a few W)
- **compact** (locate AMC with PMT)

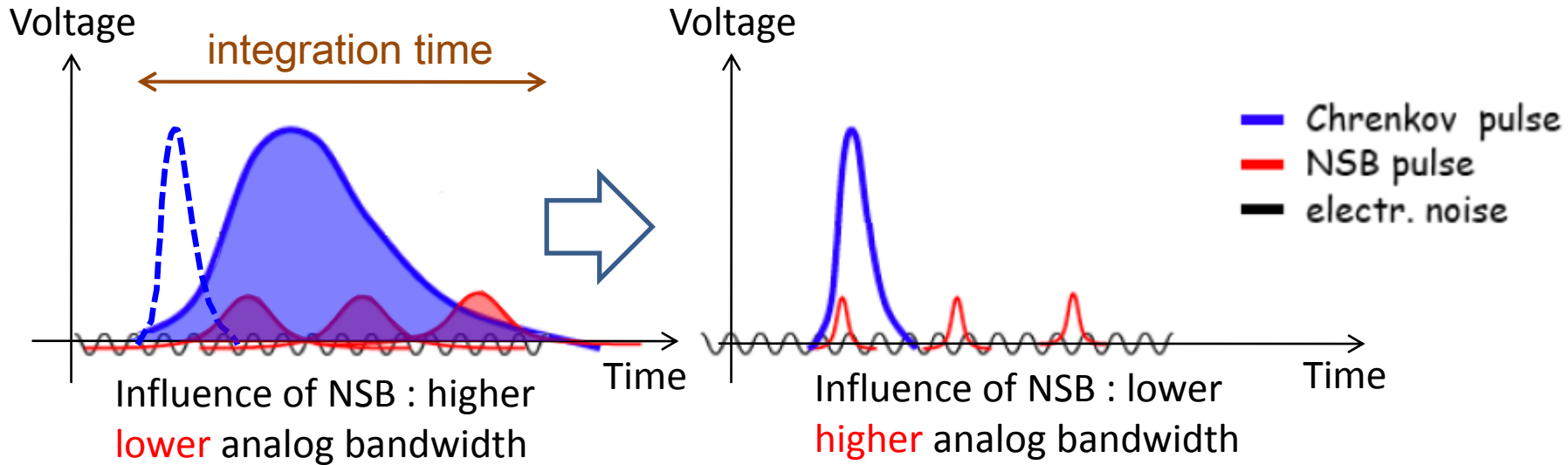
Signal to noise ratio



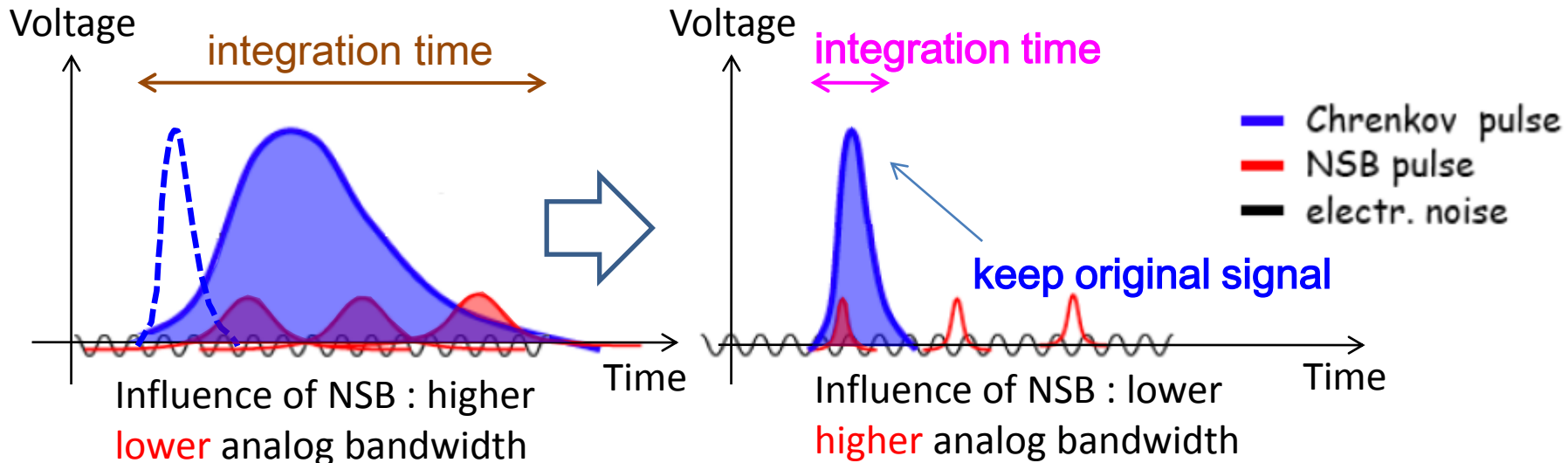
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Signal to noise ratio

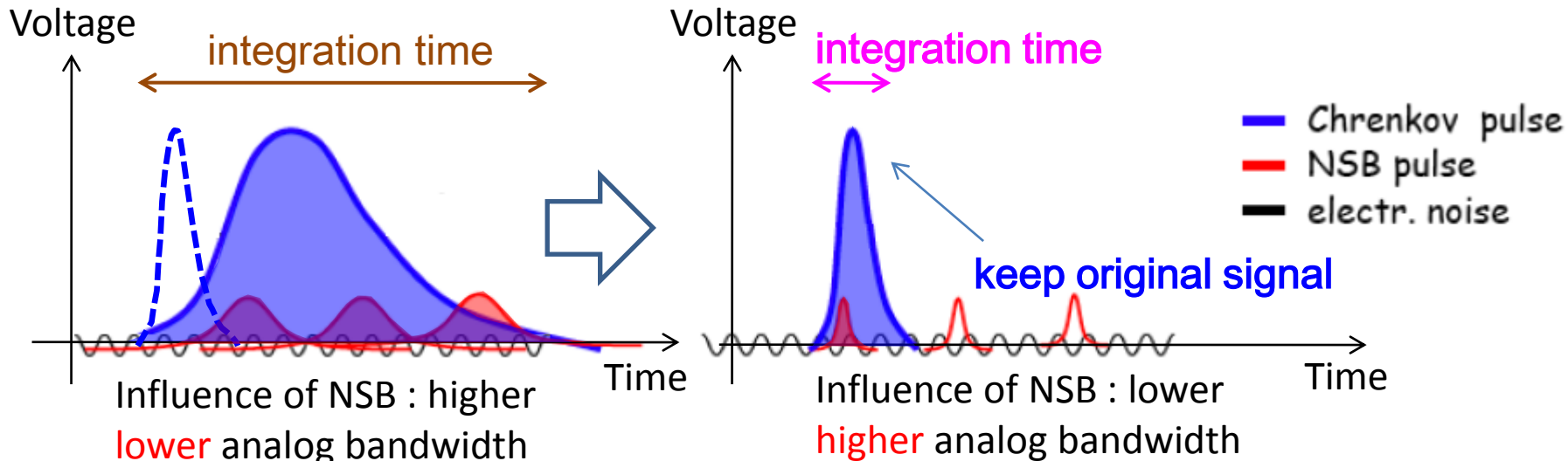


Signal to noise ratio



- Sampling with high analog bandwidth & minimizing the integration time
 - 1 reduce the influence of Night Sky Background

Signal to noise ratio



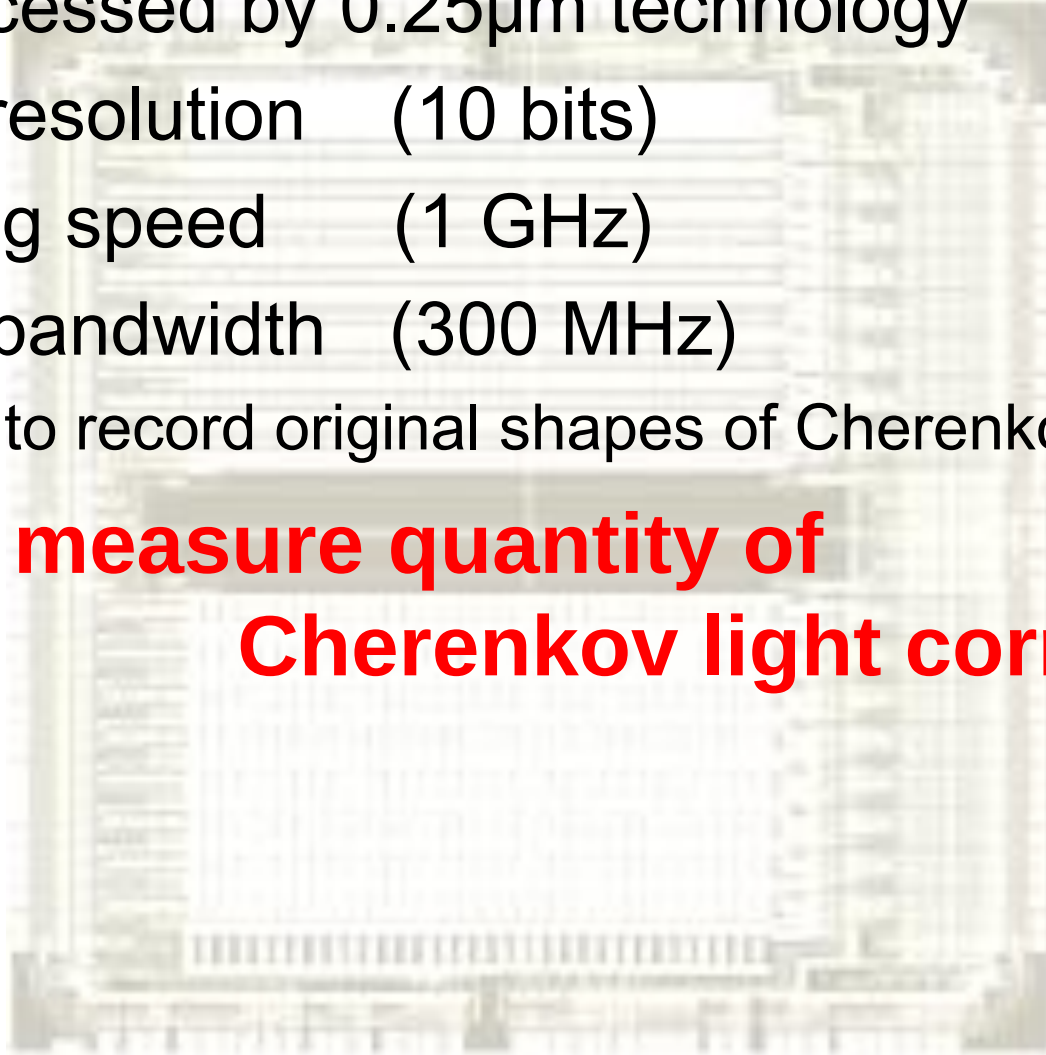
- Sampling with high analog bandwidth & minimizing the integration time
 - 1 reduce the influence of Night Sky Background
 - 2 improves shower image finer
 - 3 leads to lower threshold energy, better sensibility, better angular resolution and better energy resolution

Target specification

AMC processed by 0.25 μ m technology

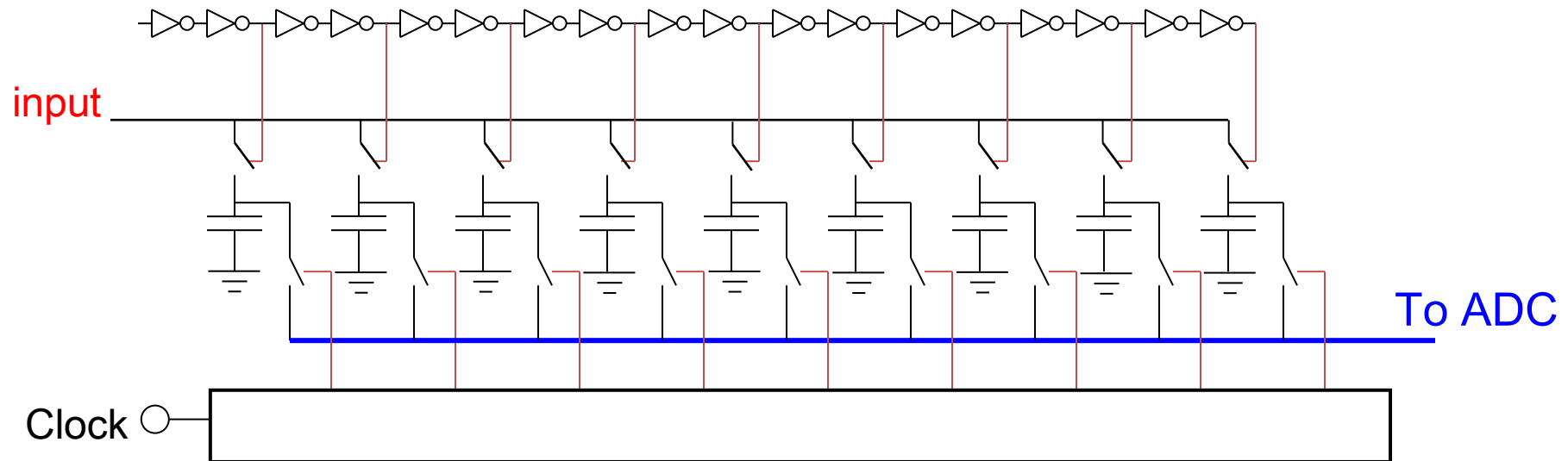
- charge resolution (10 bits)
- Sampling speed (1 GHz)
- Analog bandwidth (300 MHz)
 - enough to record original shapes of Cherenkov light signals

**We can measure quantity of
Cherenkov light correctly**



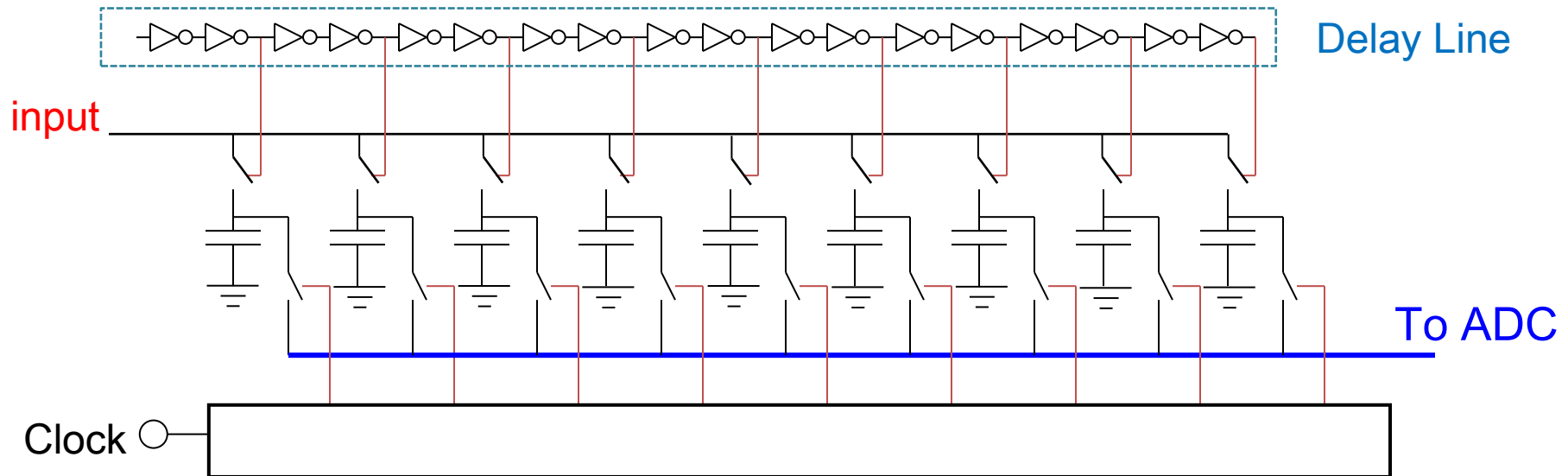
How AMC sample voltage

- AMC has mainly



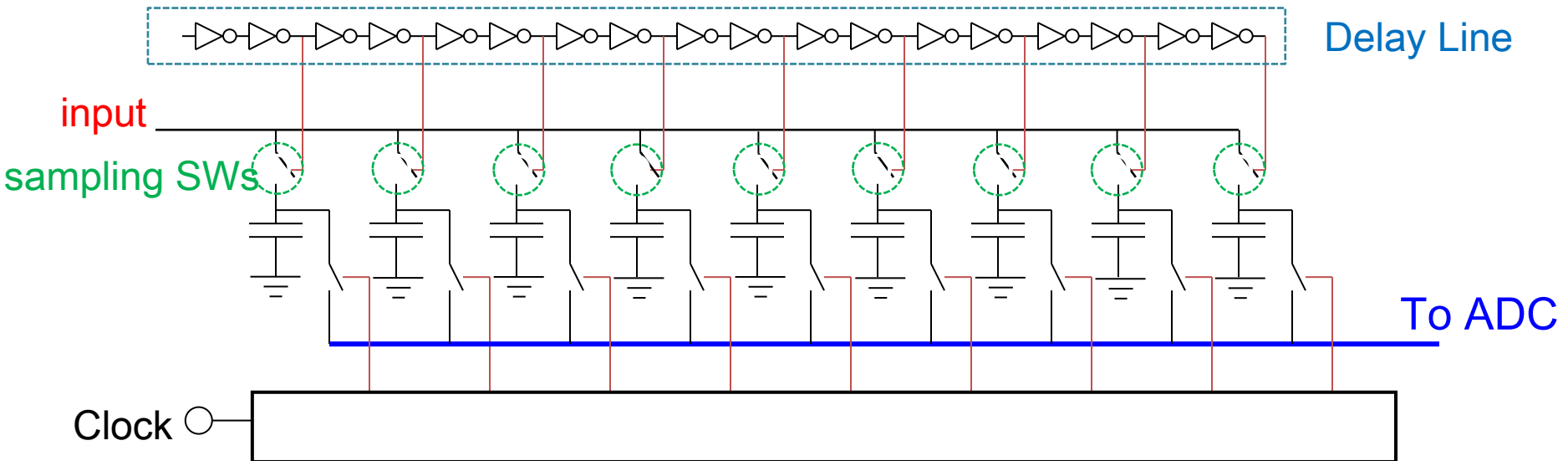
How AMC sample voltage

- AMC has mainly
delay line (CMOS inverter)



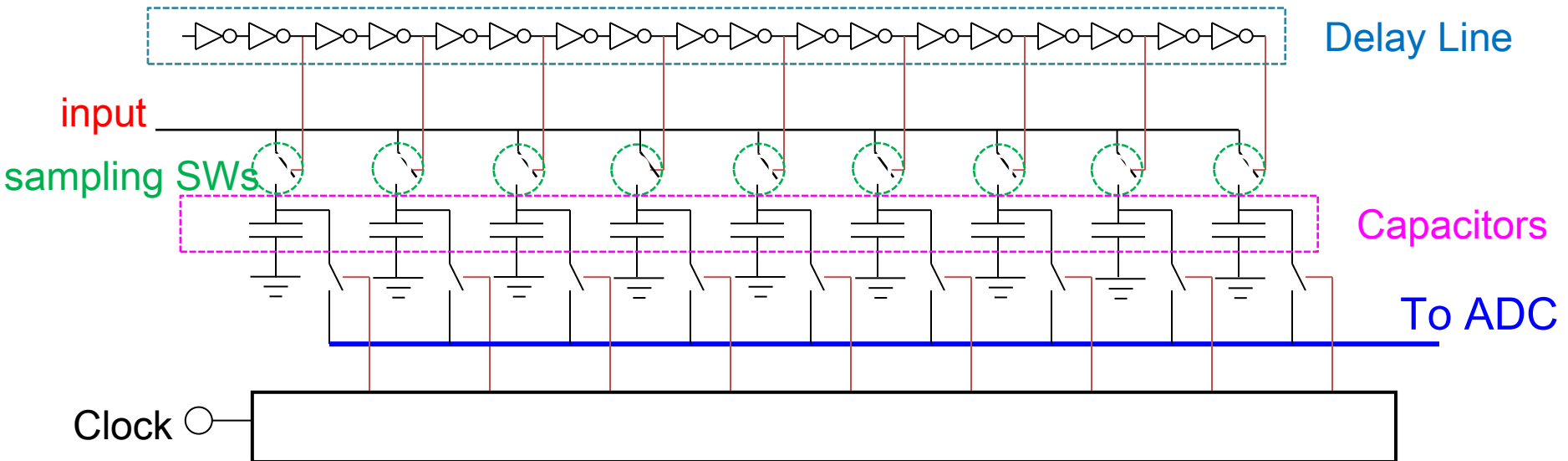
How AMC sample voltage

- AMC has mainly
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sampling SWs (MOSFET)



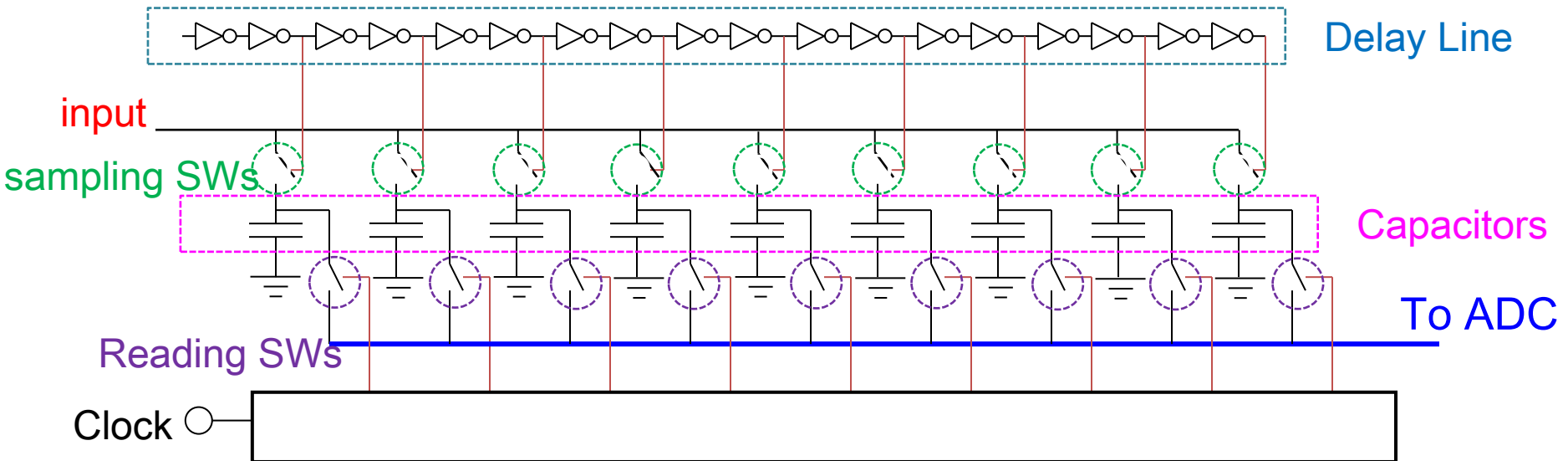
How AMC sample voltage

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capacitors



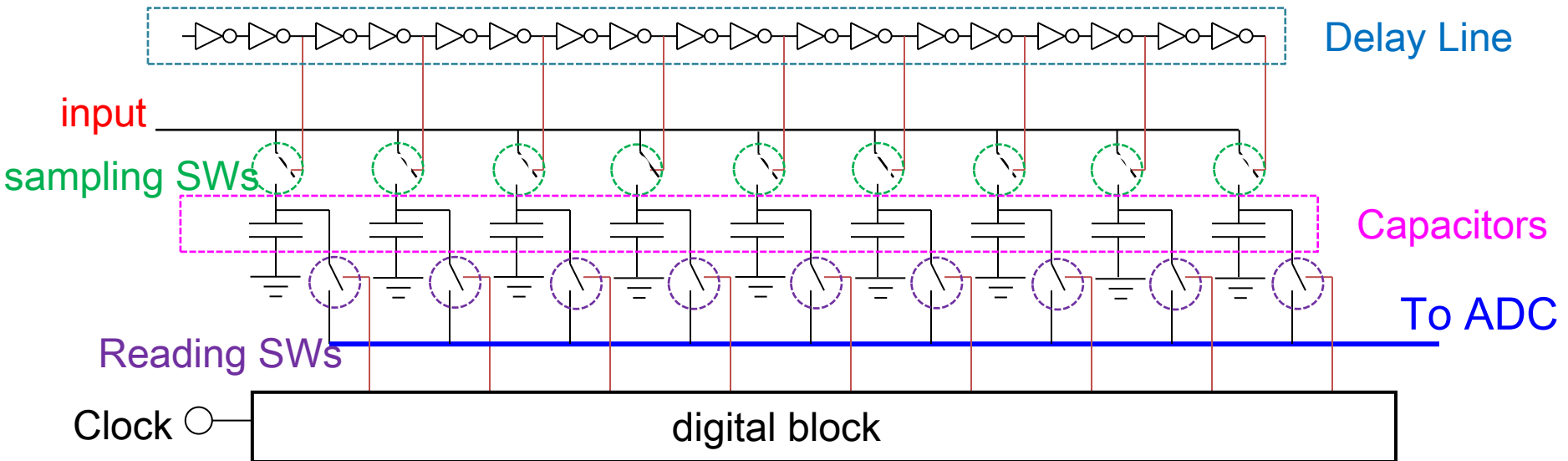
How AMC sample voltage

- AMC has mainly
 - delay line (CMOS inverter)
 - sampling SWs (MOSFET)
 - capacitors
 - reading SWs (MOSFET)



How AMC sample voltage

- AMC has mainly
 - delay line (CMOS inverter)
 - sampling SWs (MOSFET)
 - capacitors
 - reading SWs (MOSFET)
 - digital block

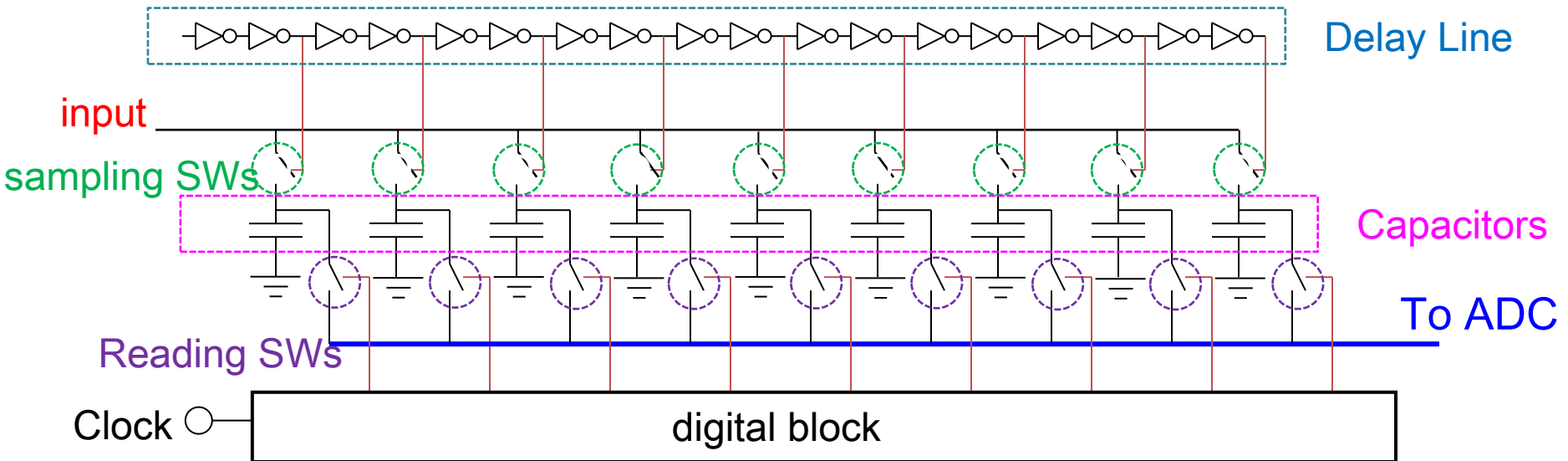


How AMC sample voltage

① Sampling mode

② Reading mode

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capacitors
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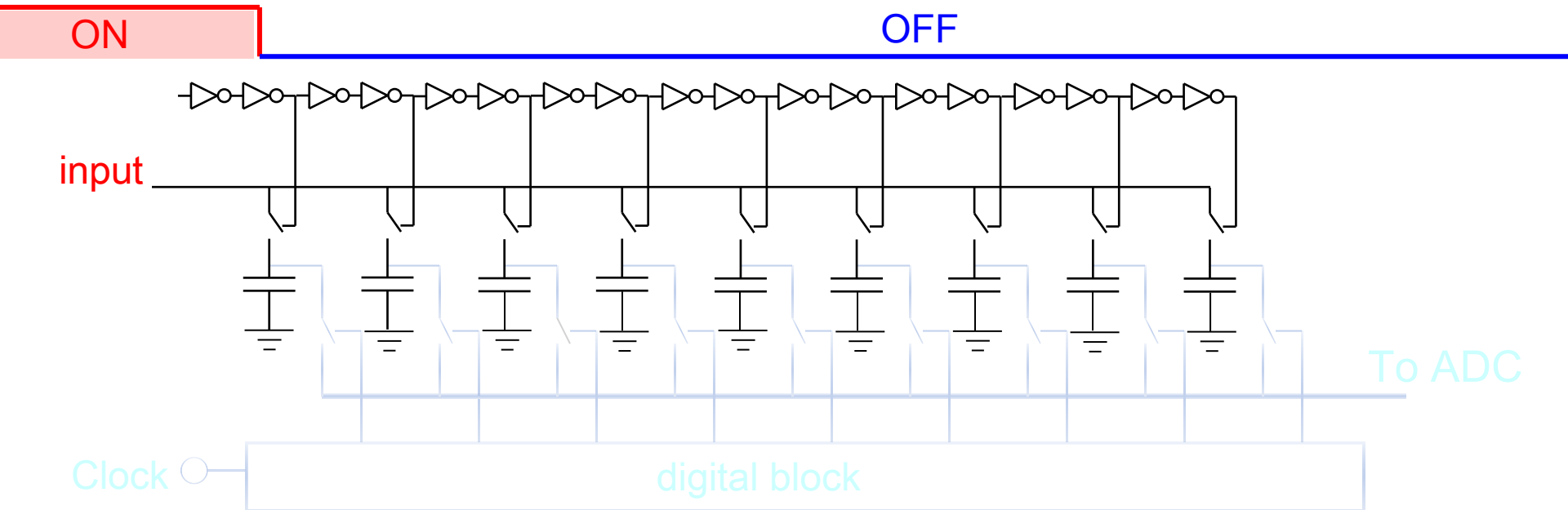
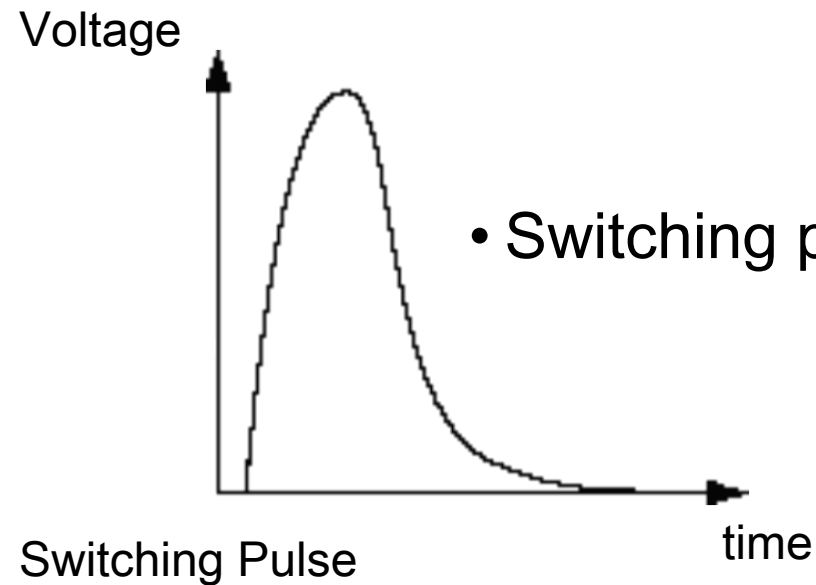


How AMC sample voltage

① Sampling mode

② Reading mode

- Switching pulse makes SWs **ON** and **OFF** 1 by 1

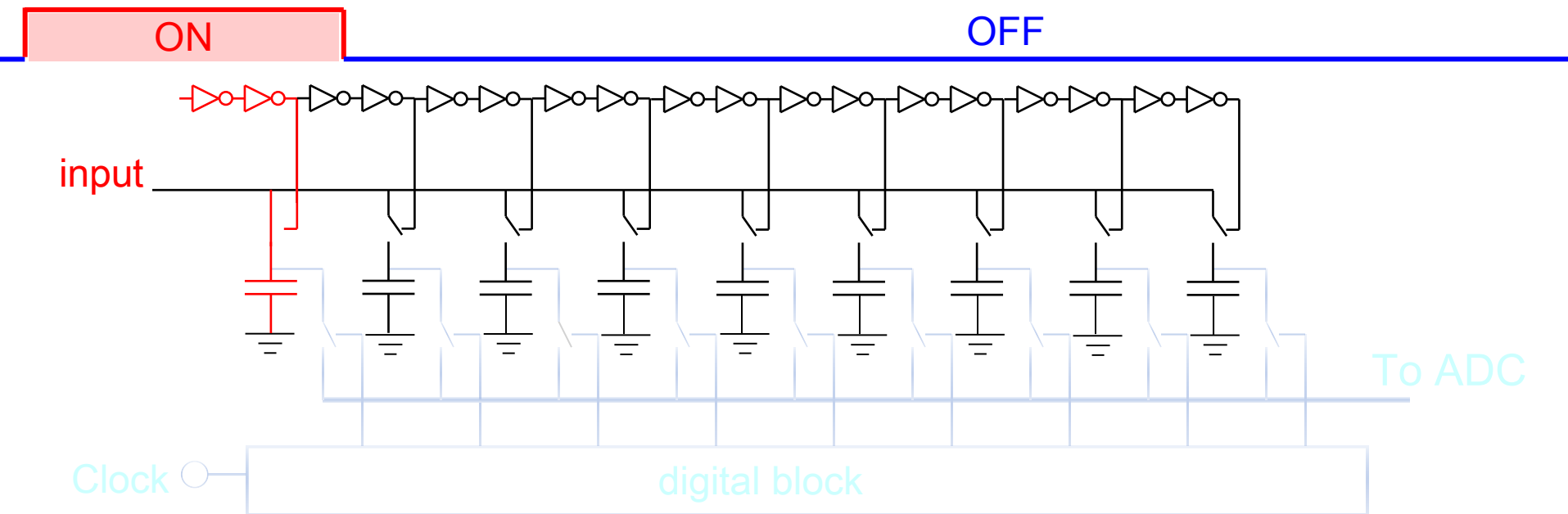
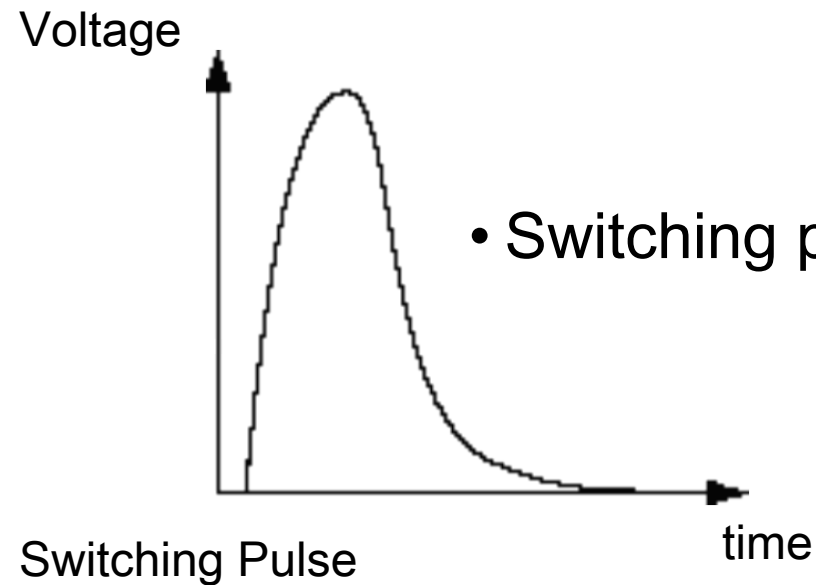


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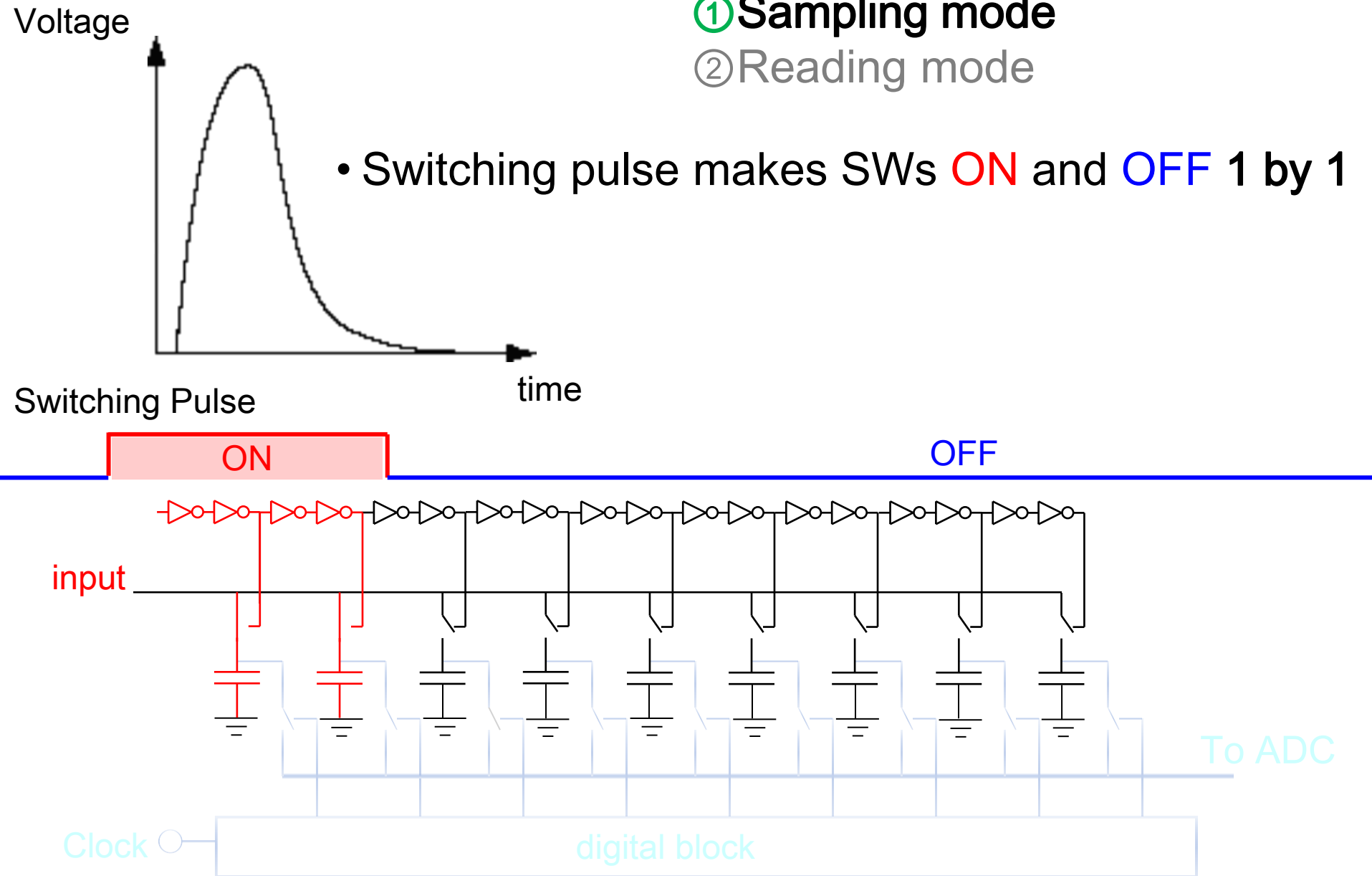


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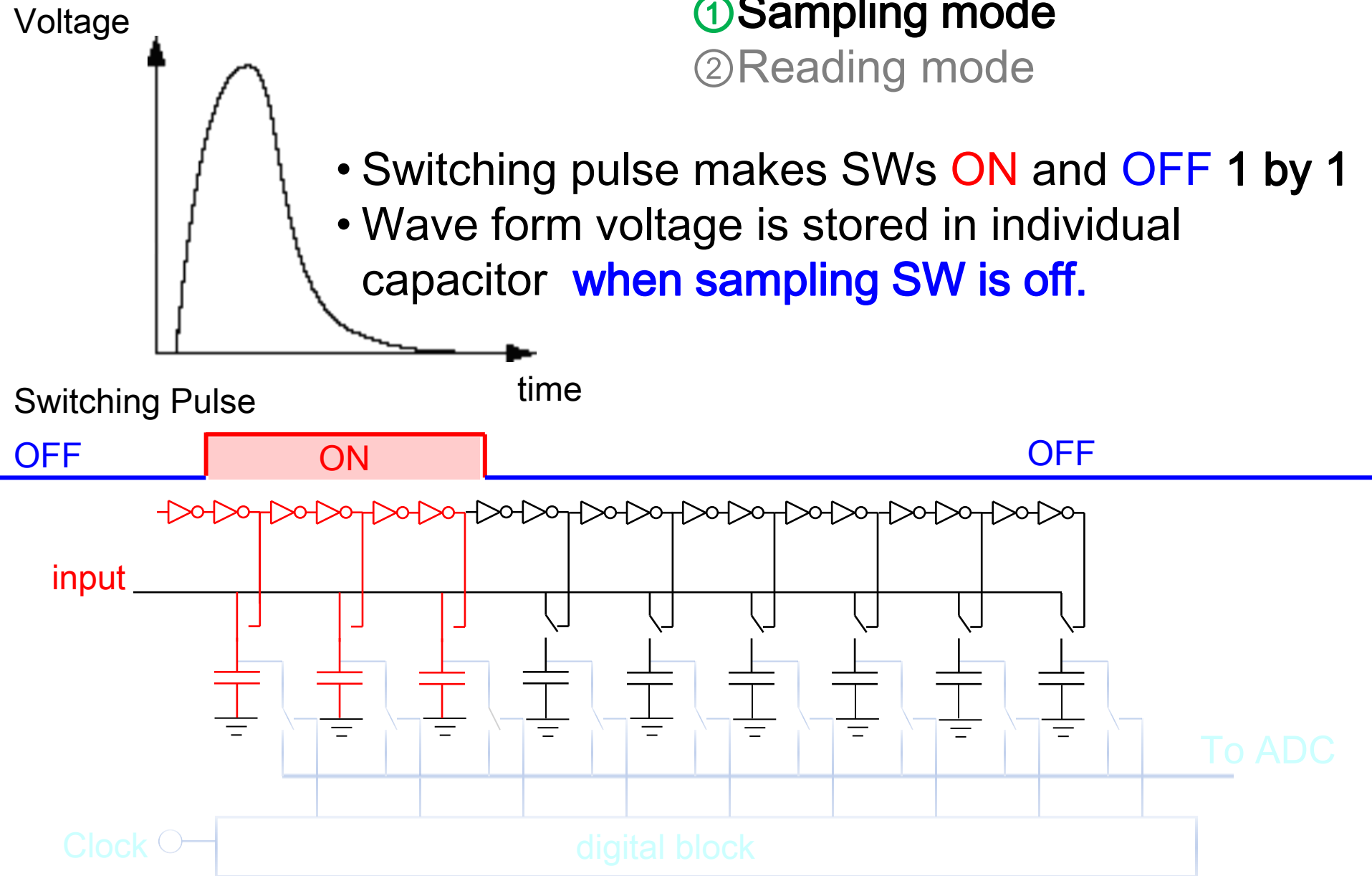


How AMC sample voltage

① Sampling mode

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- Switching pulse makes SWs **ON** and **OFF** 1 by 1
- Wave form voltage is stored in individual capacitor **when sampling SW is off.**

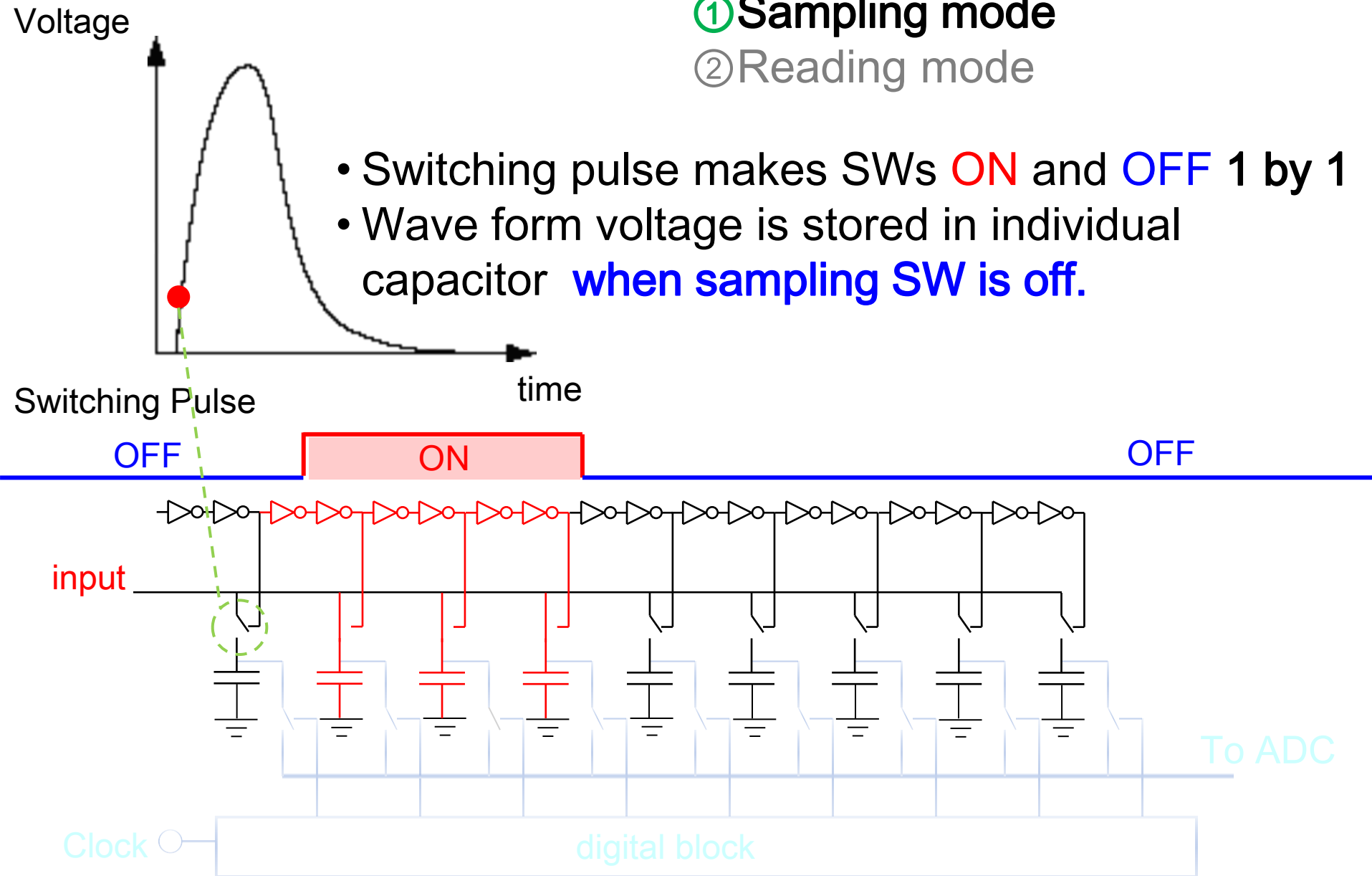


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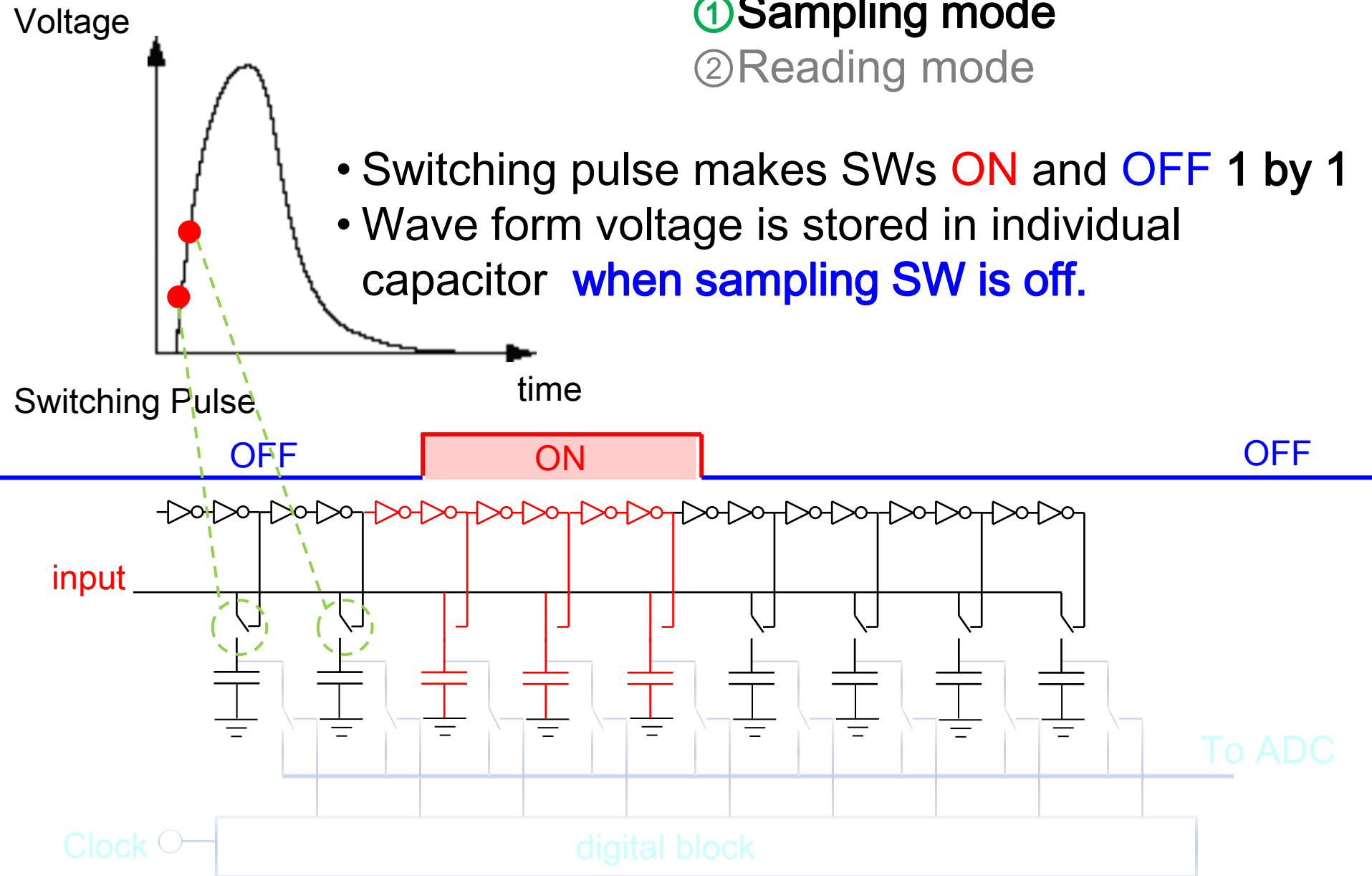


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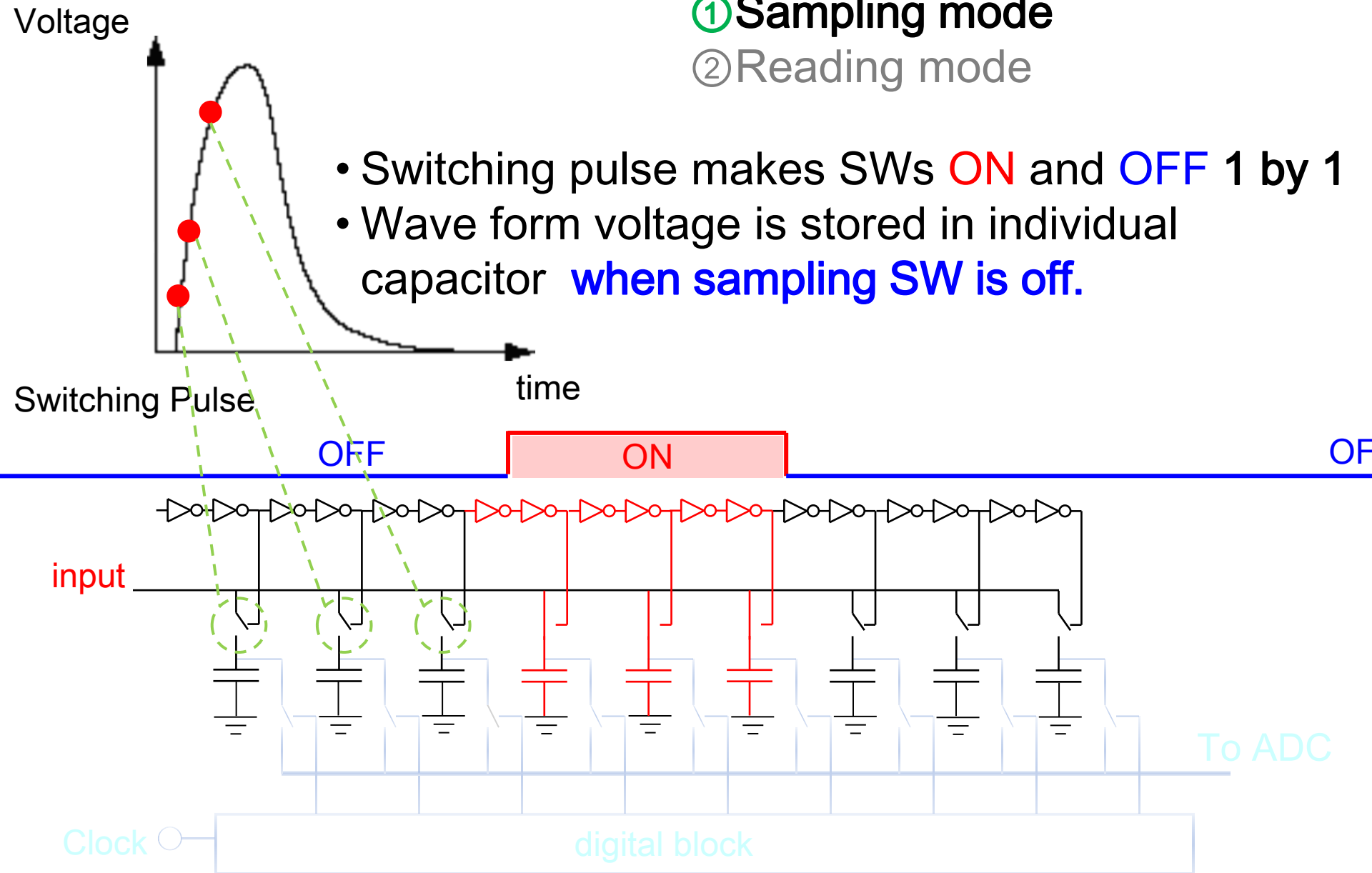


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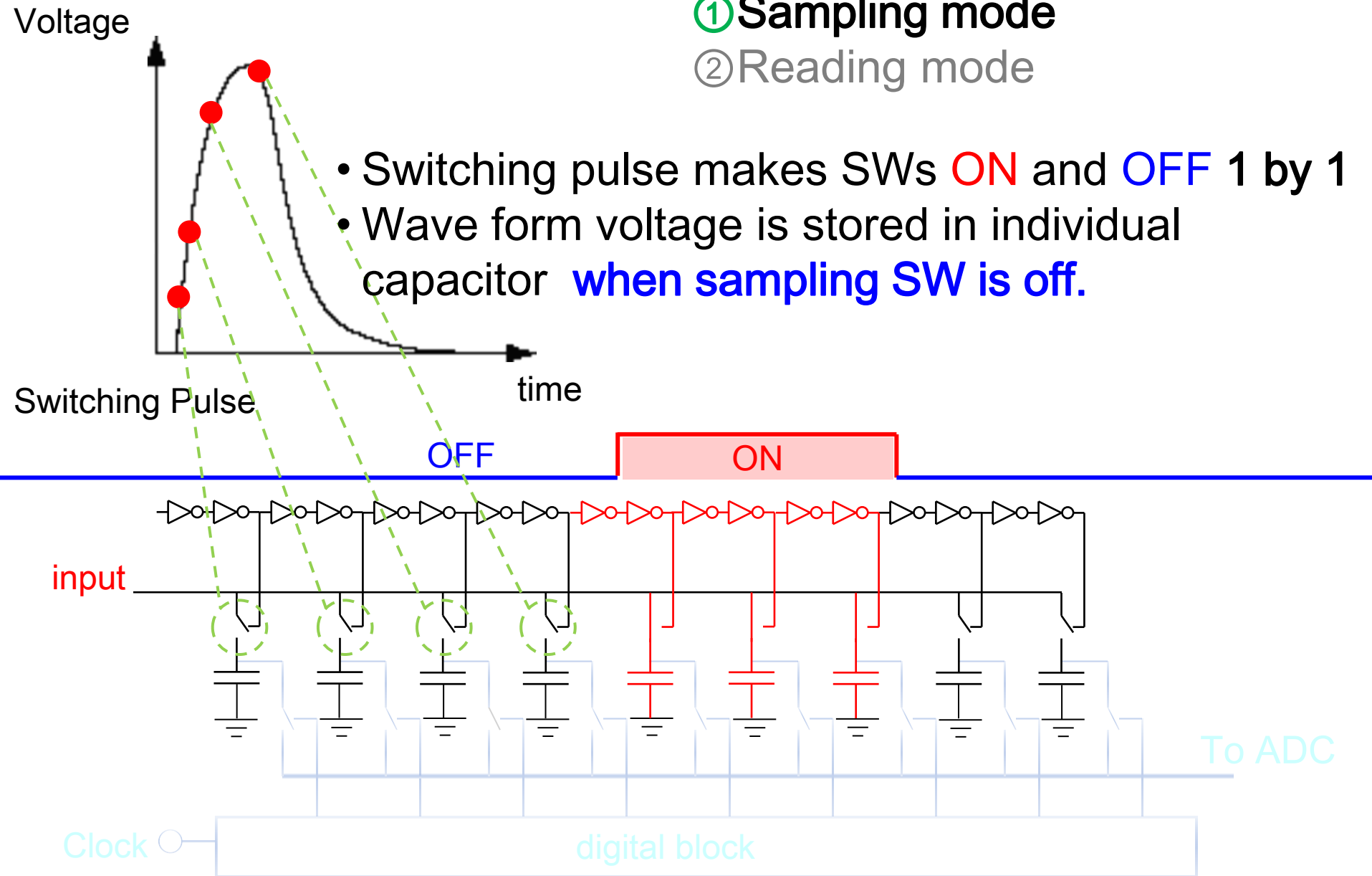


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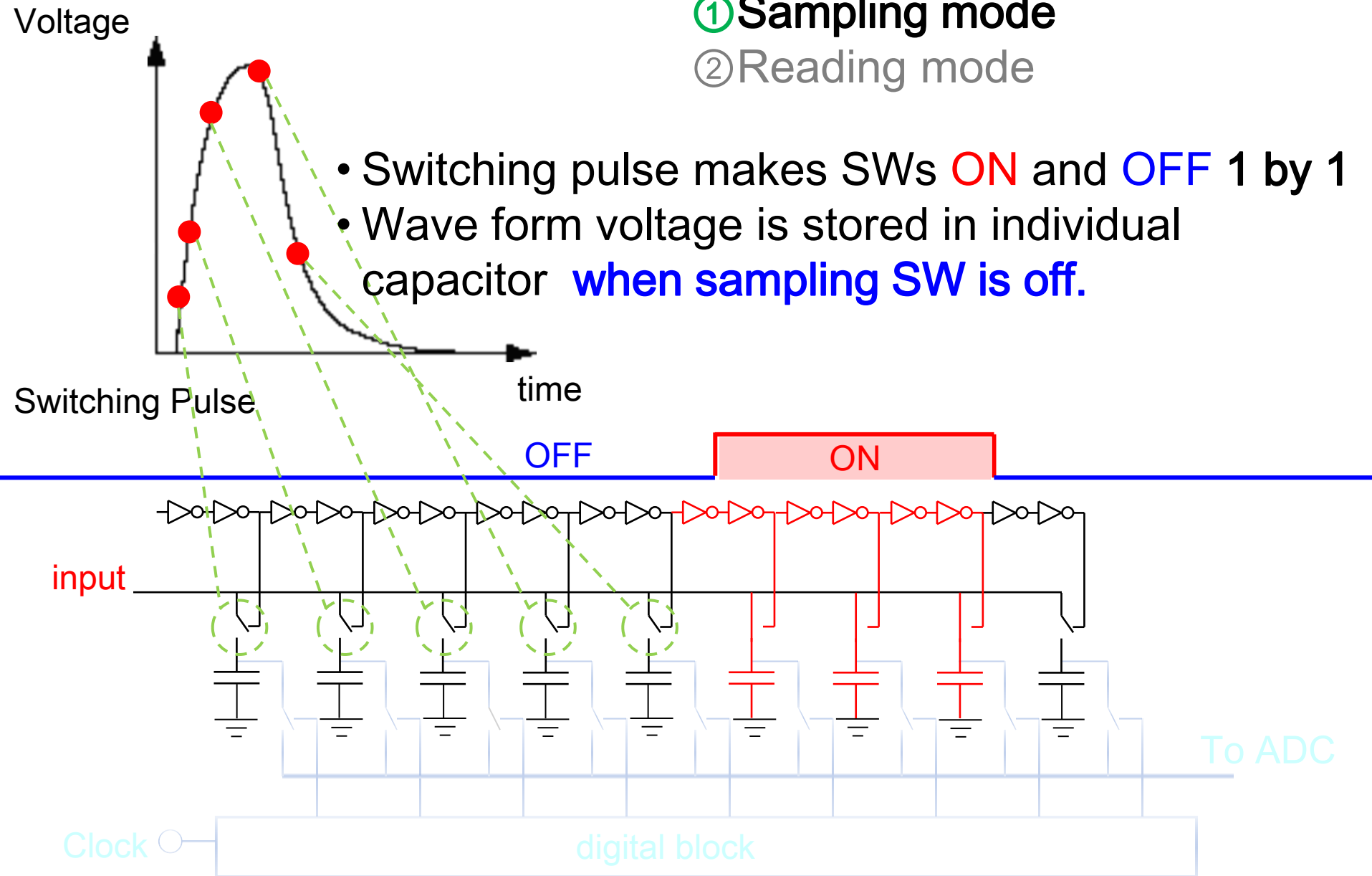


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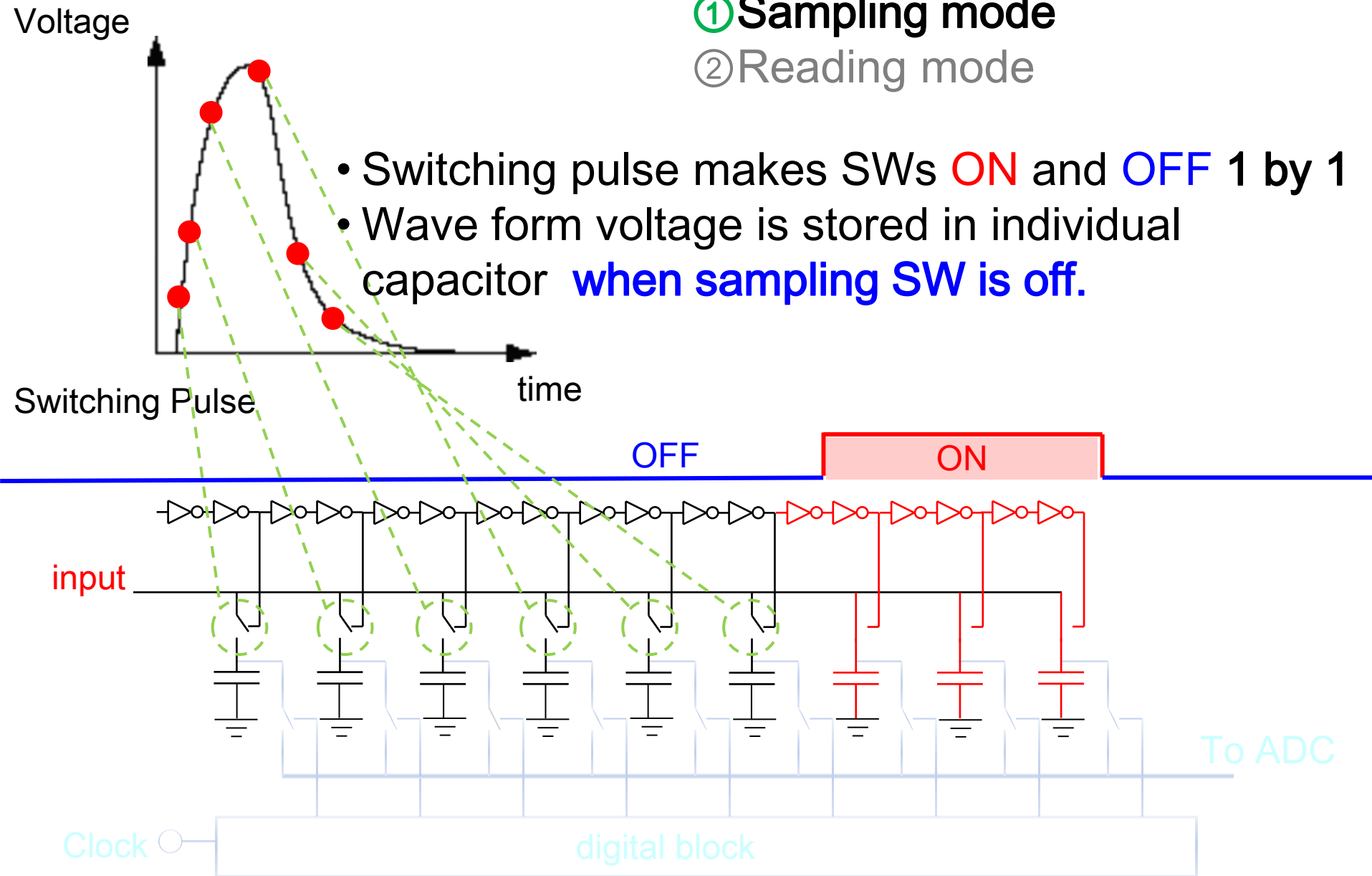


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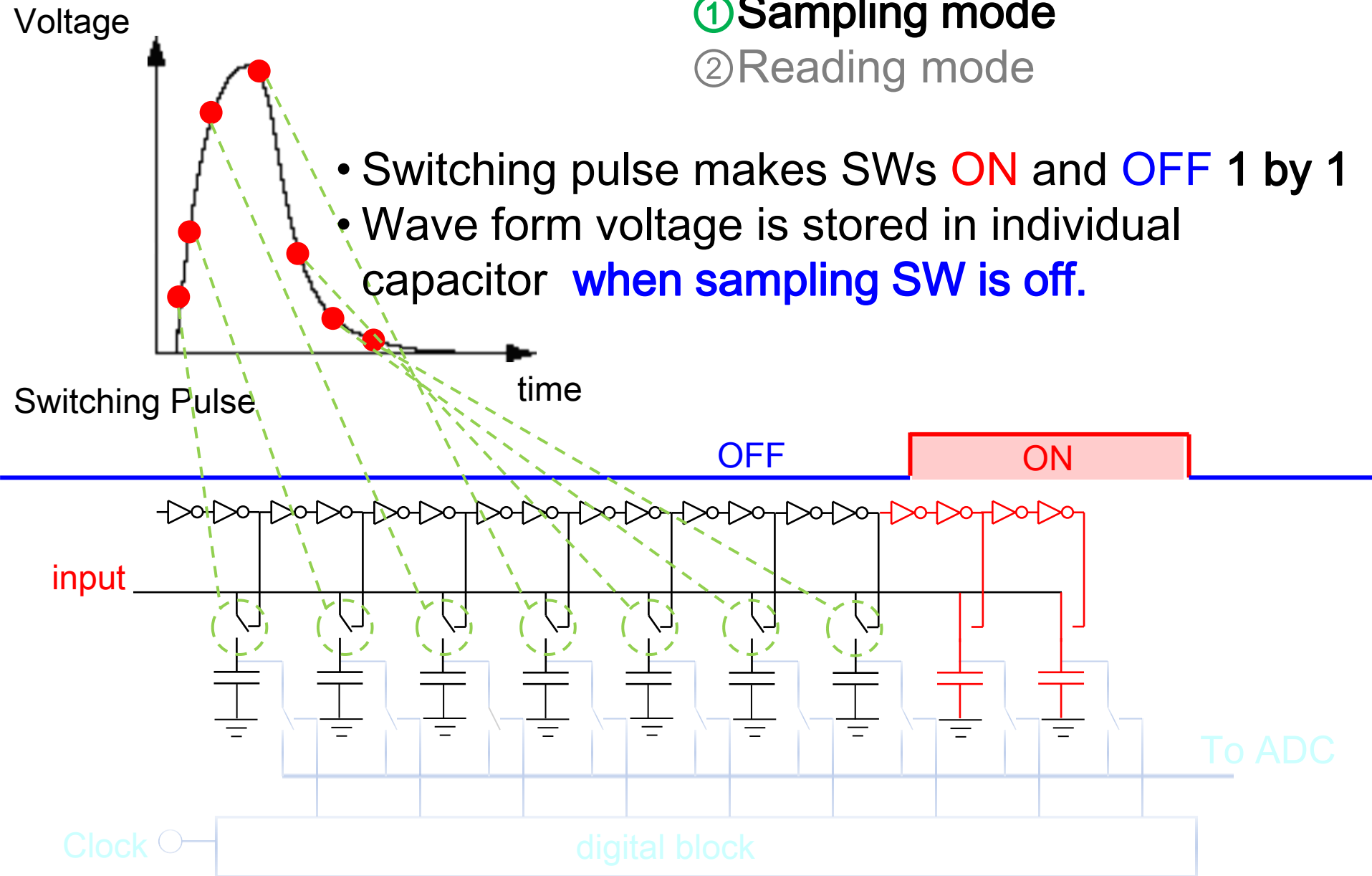


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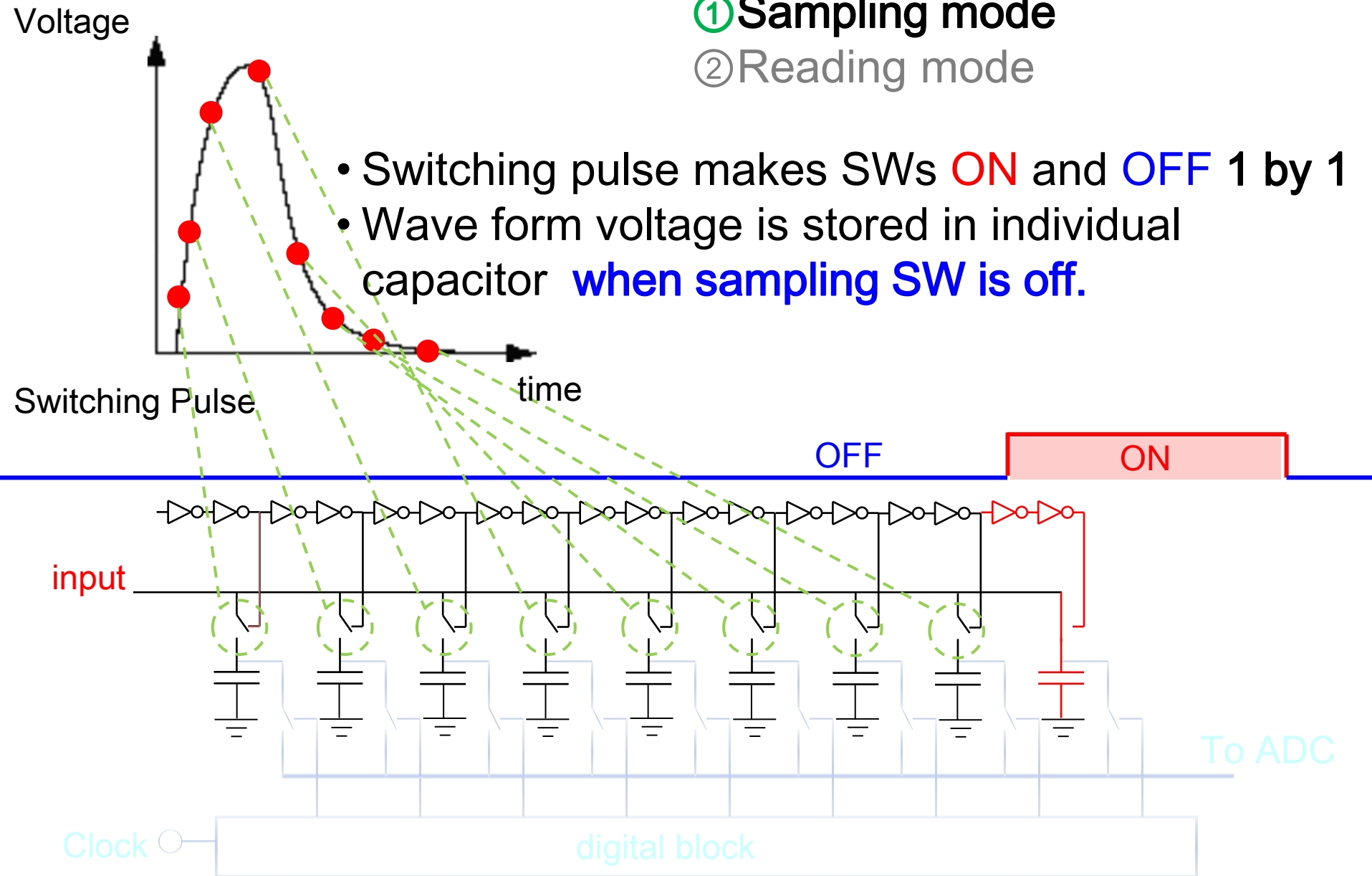


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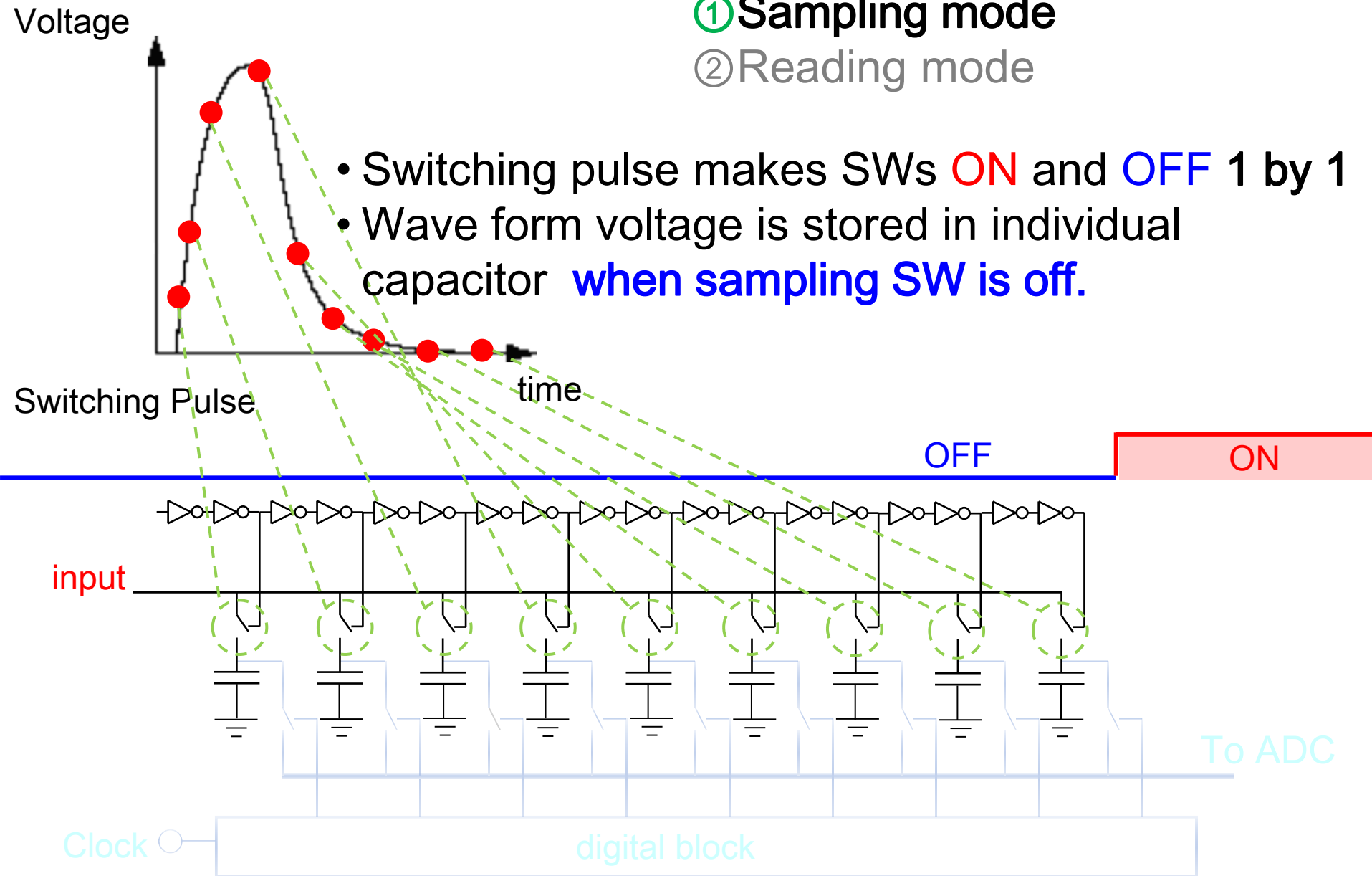


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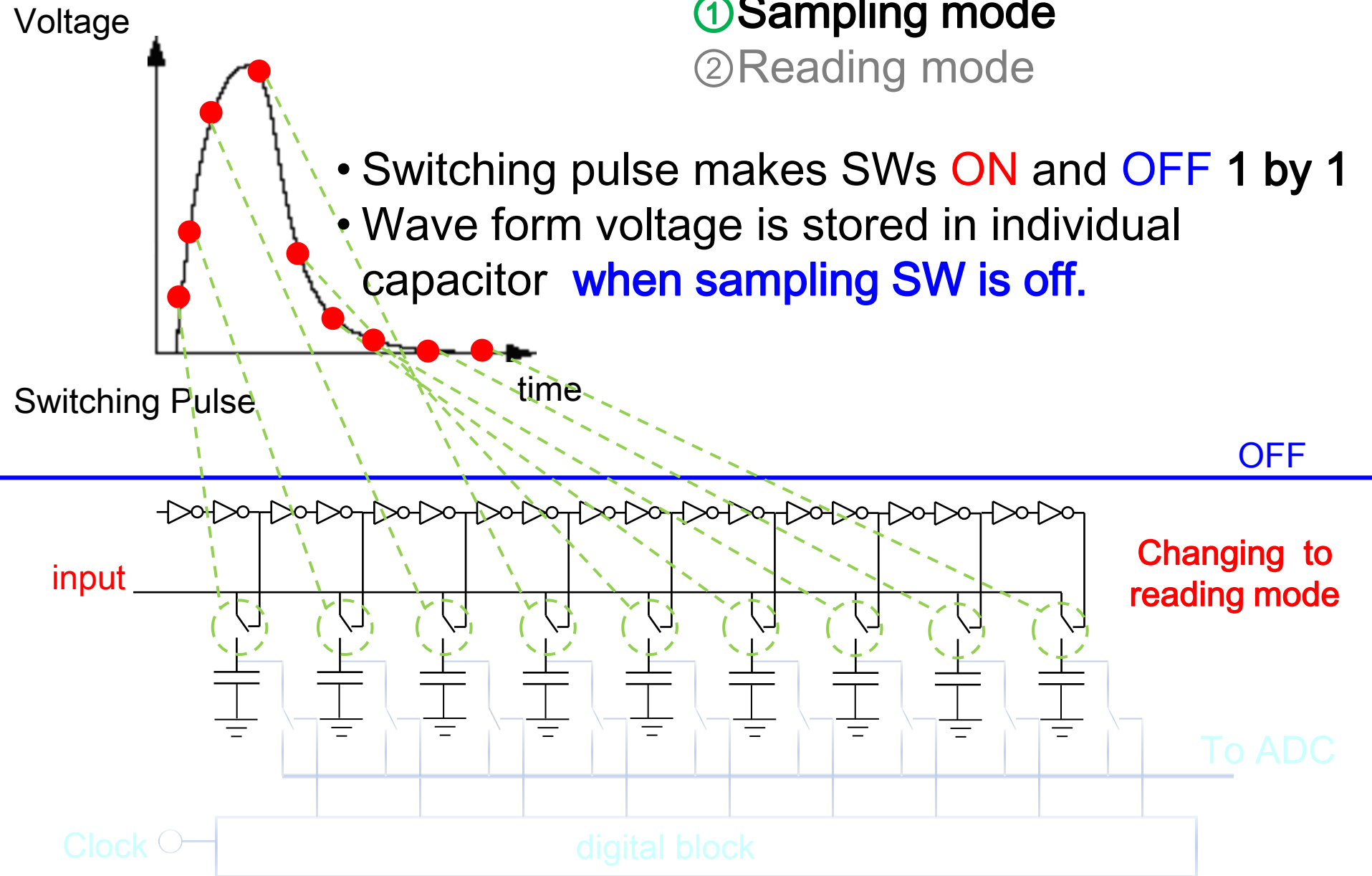


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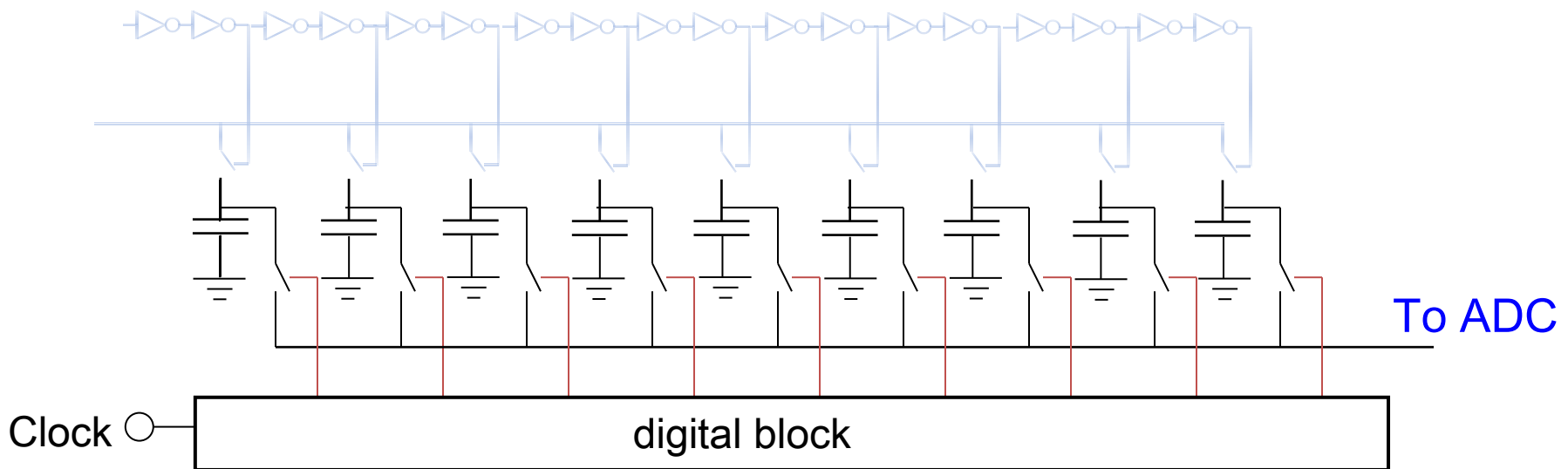
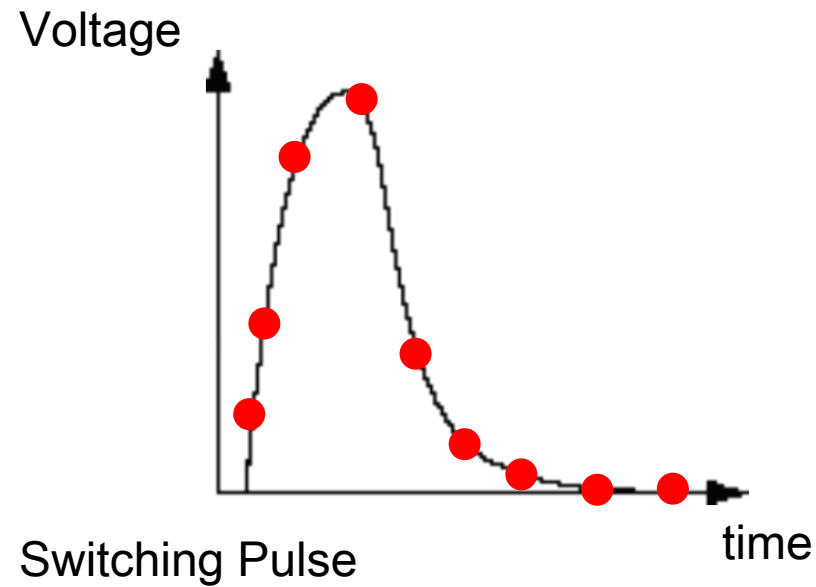
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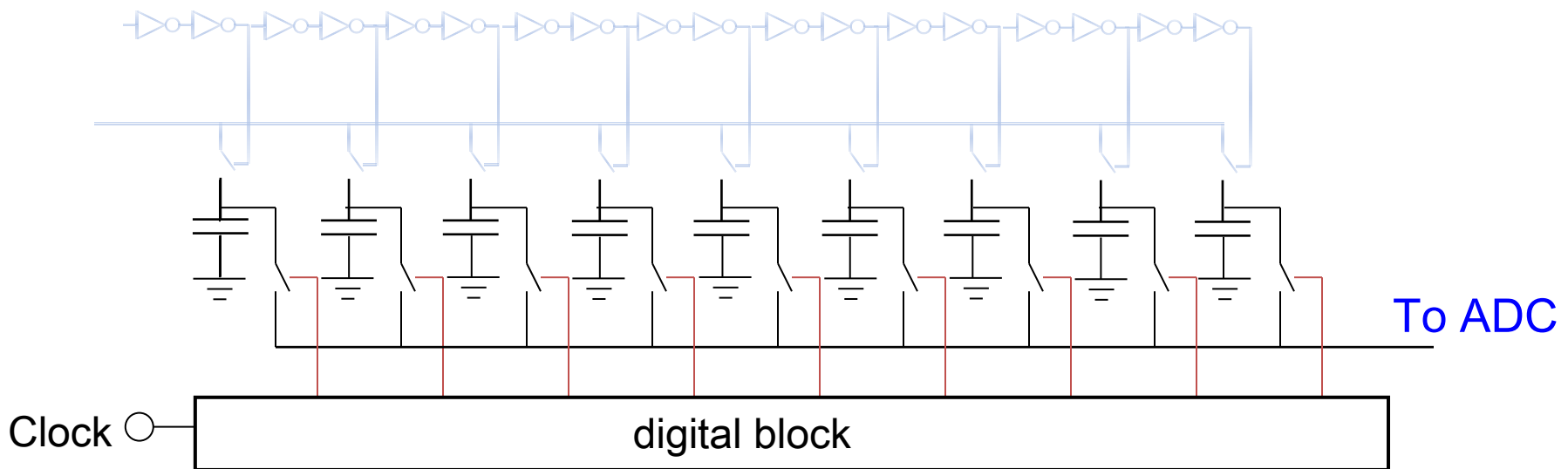
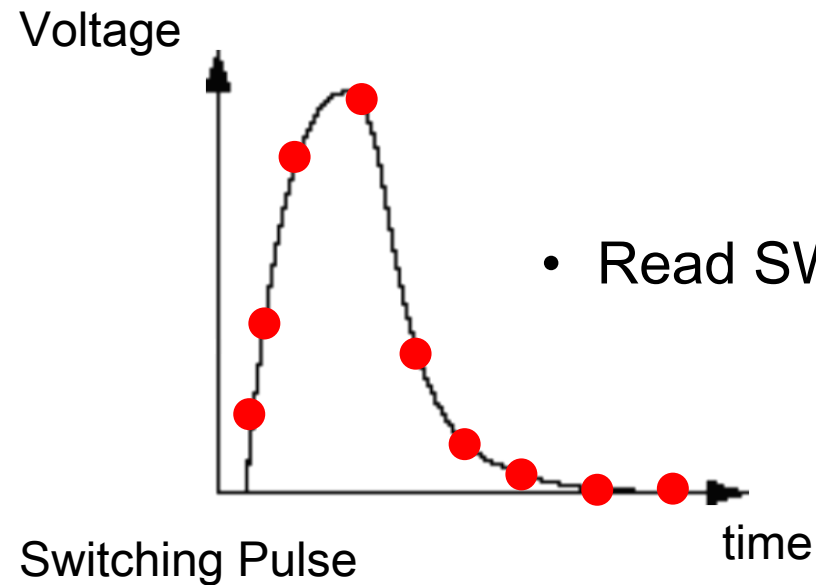


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- Read SWs are ON 1 by 1 to digitize stored data

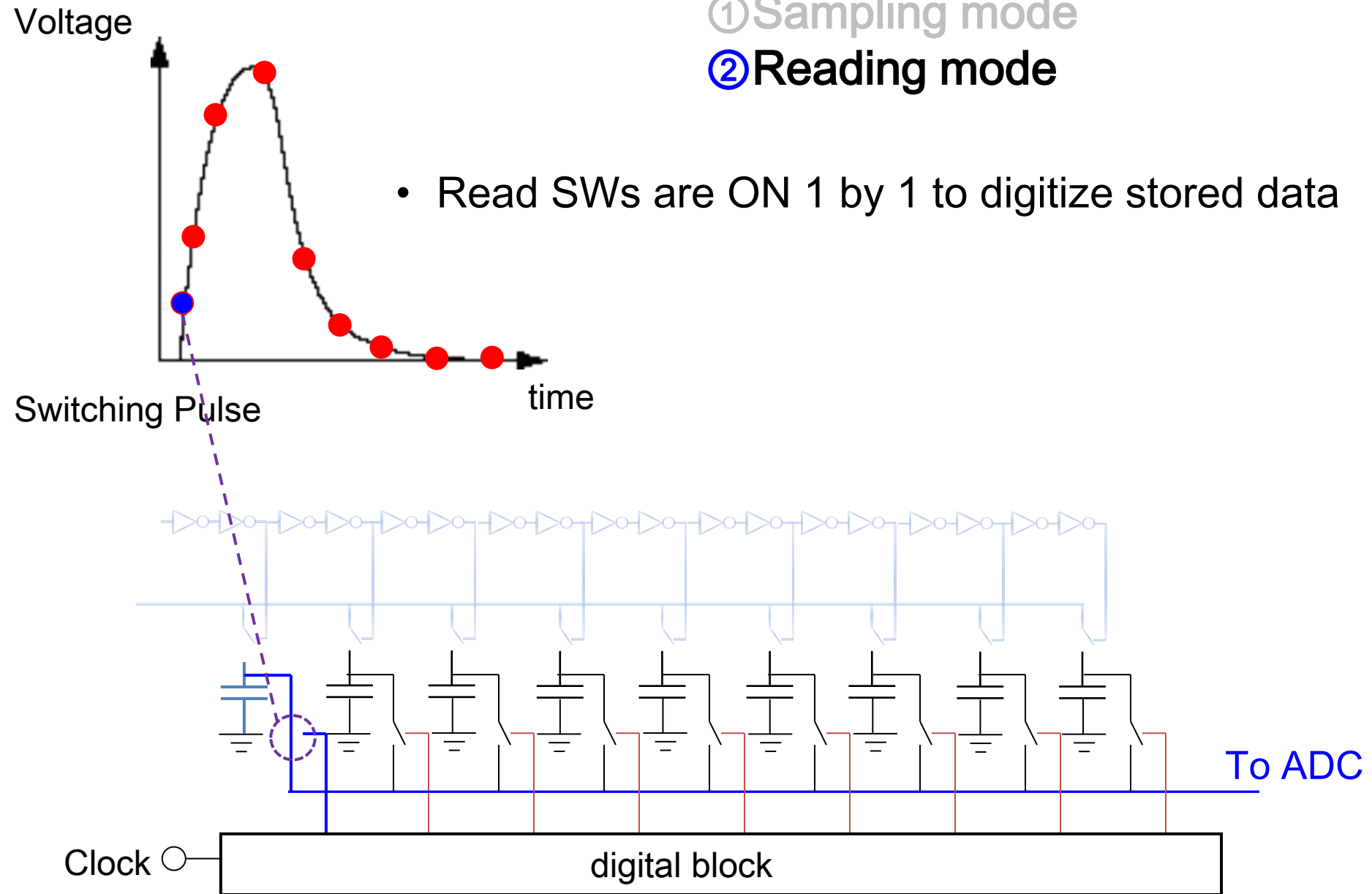


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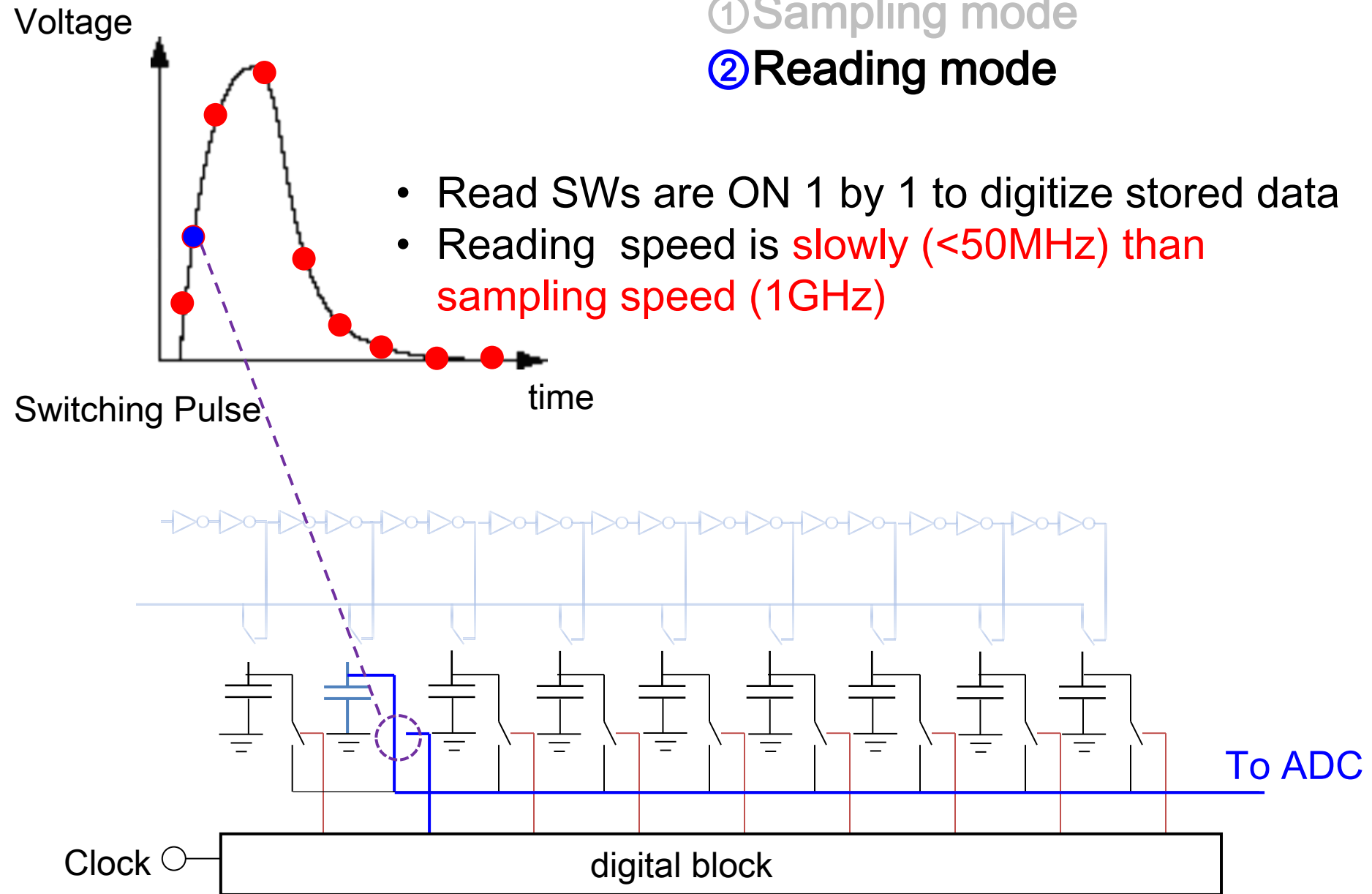


How AMC sample voltage

① Sampling mode

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- Read SWs are ON 1 by 1 to digitize stored data
- Reading speed is **slowly (<50MHz)** than **sampling speed (1GHz)**

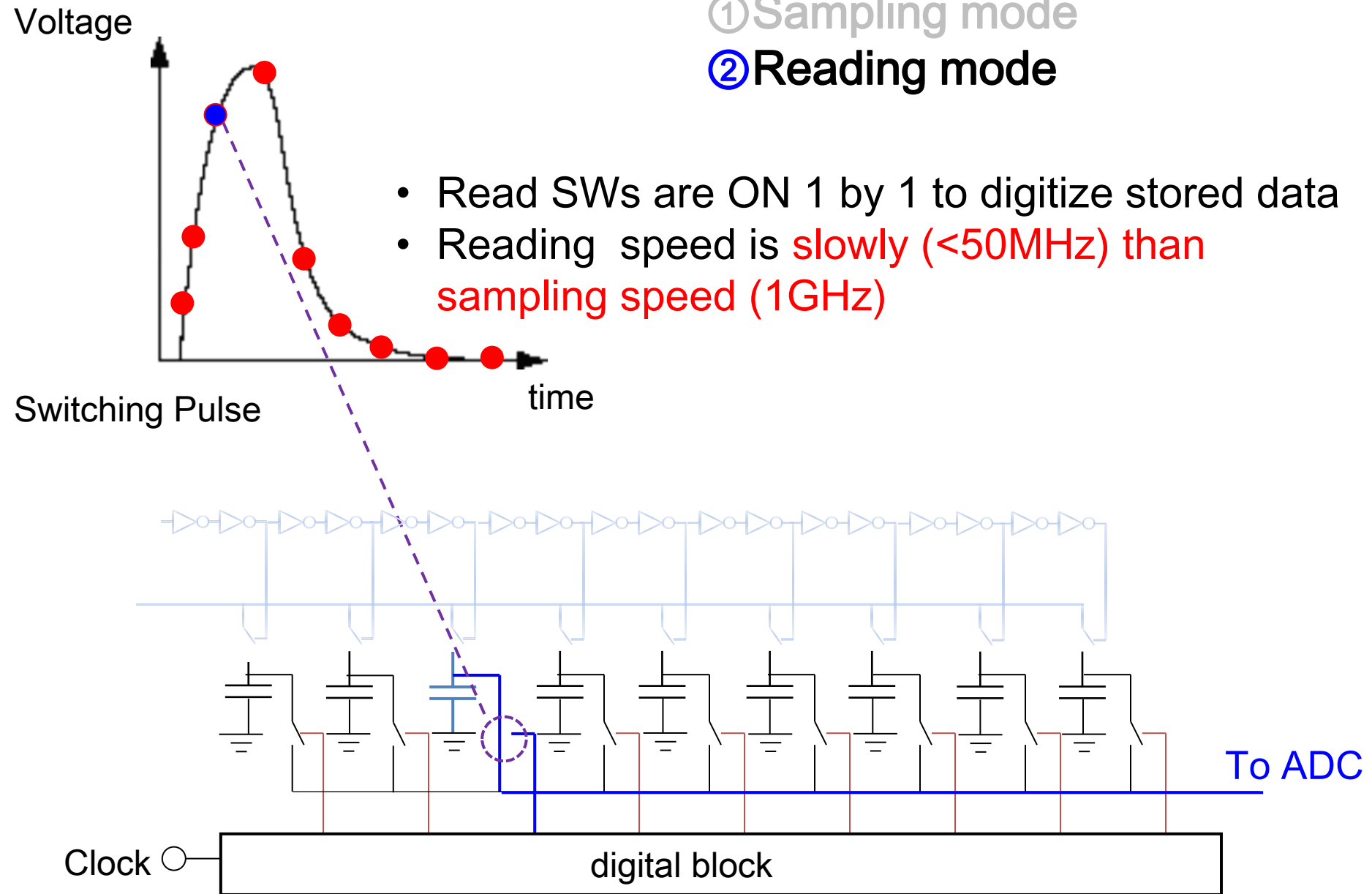


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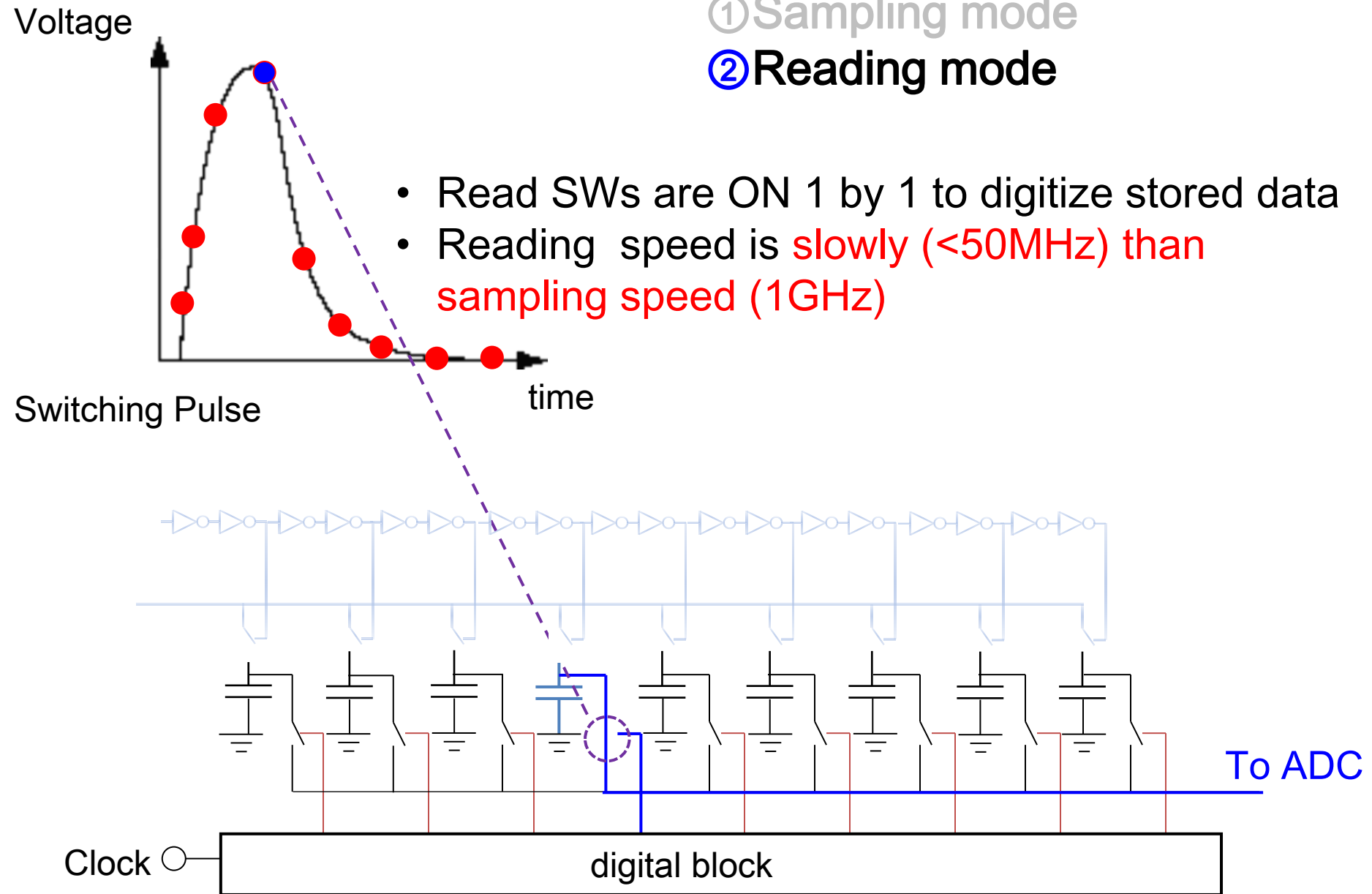


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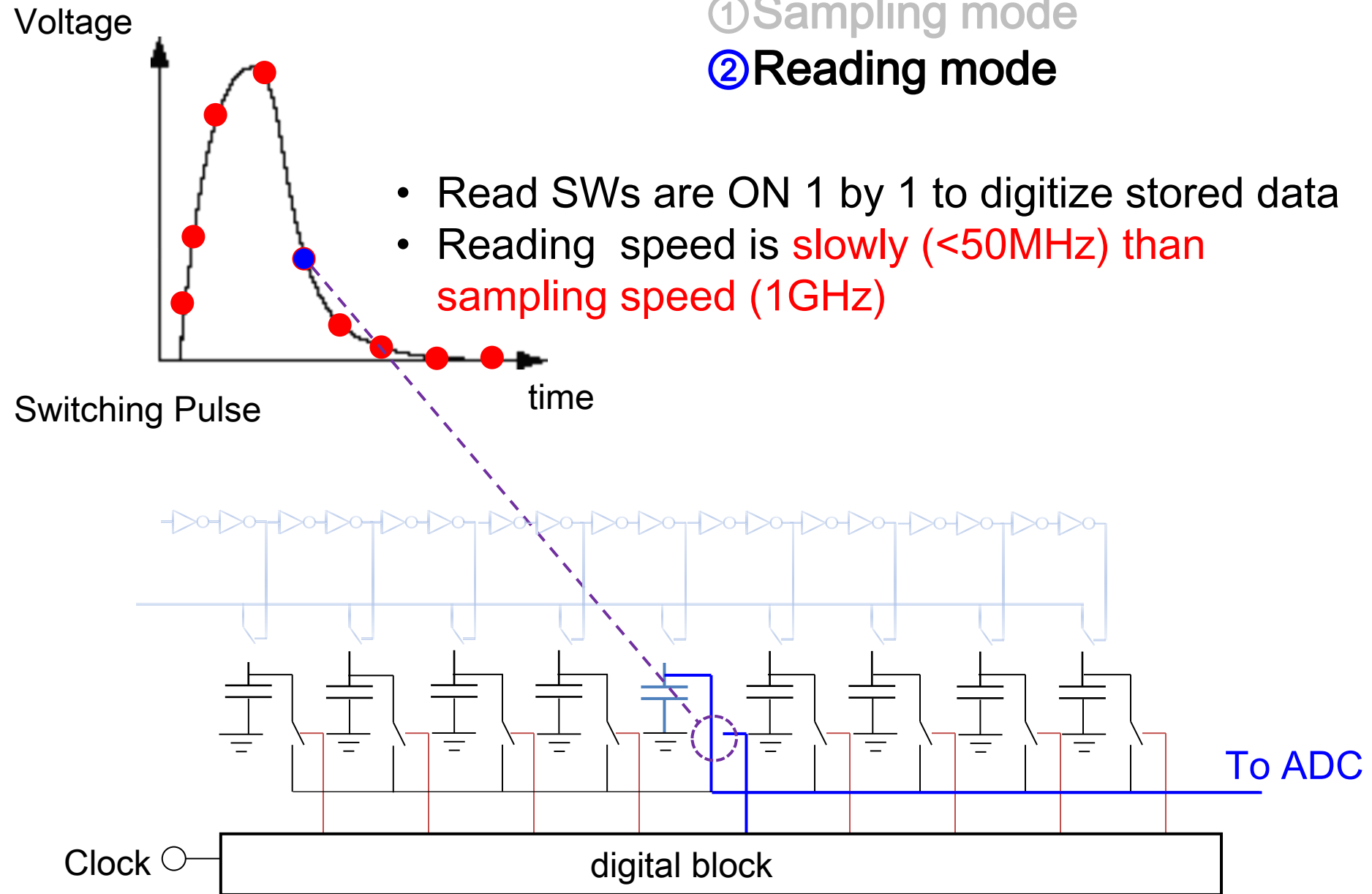


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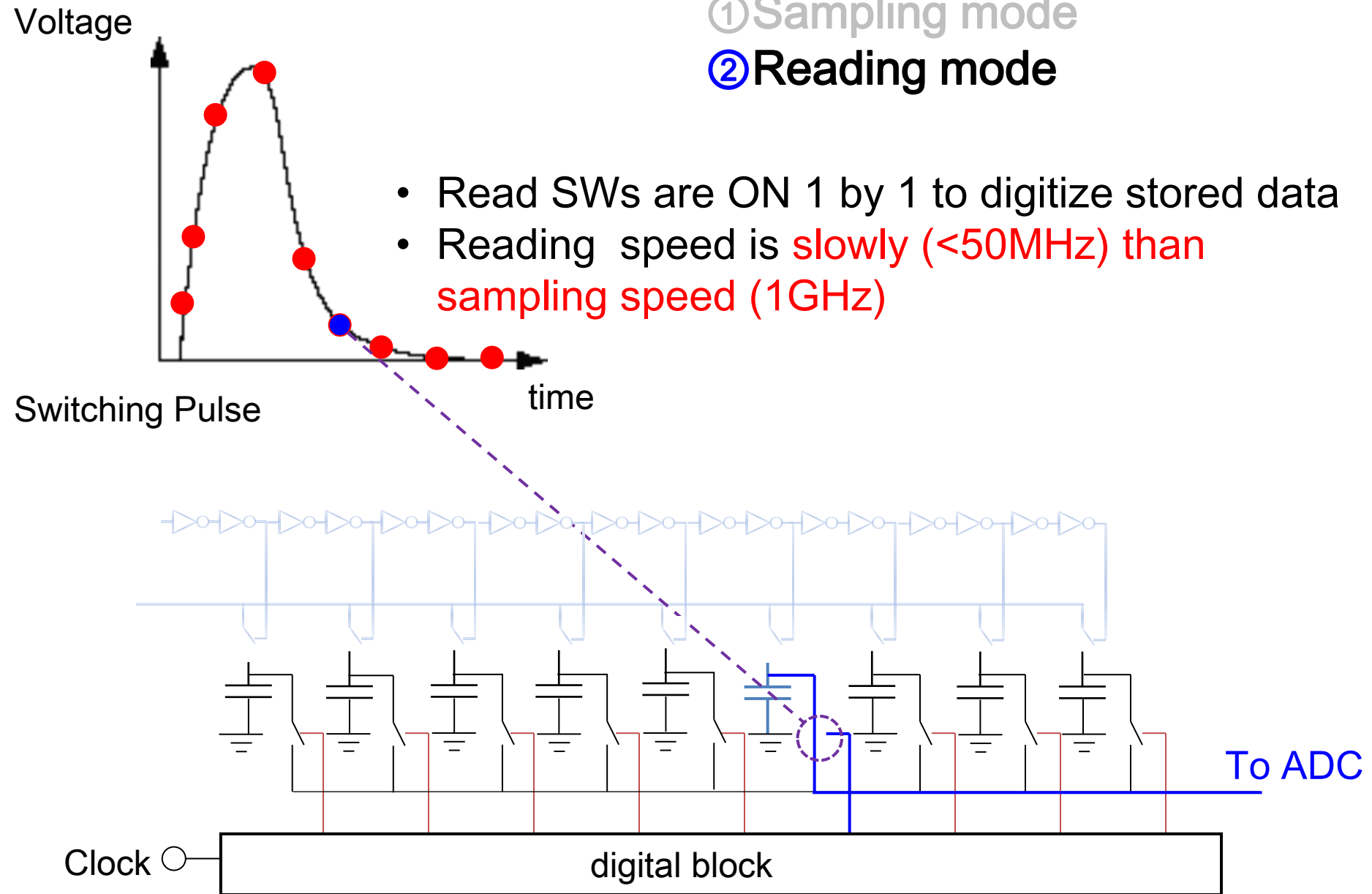


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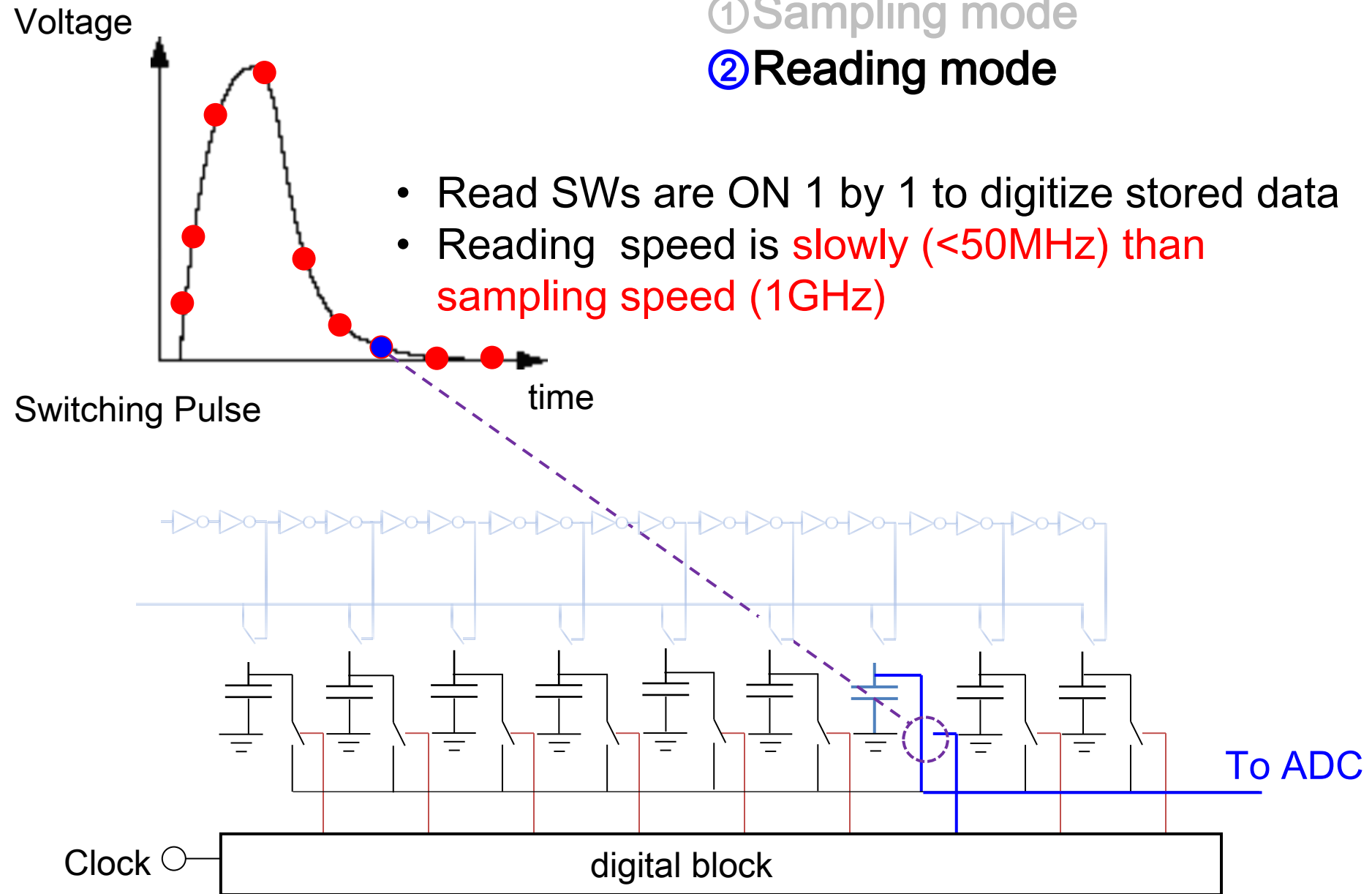


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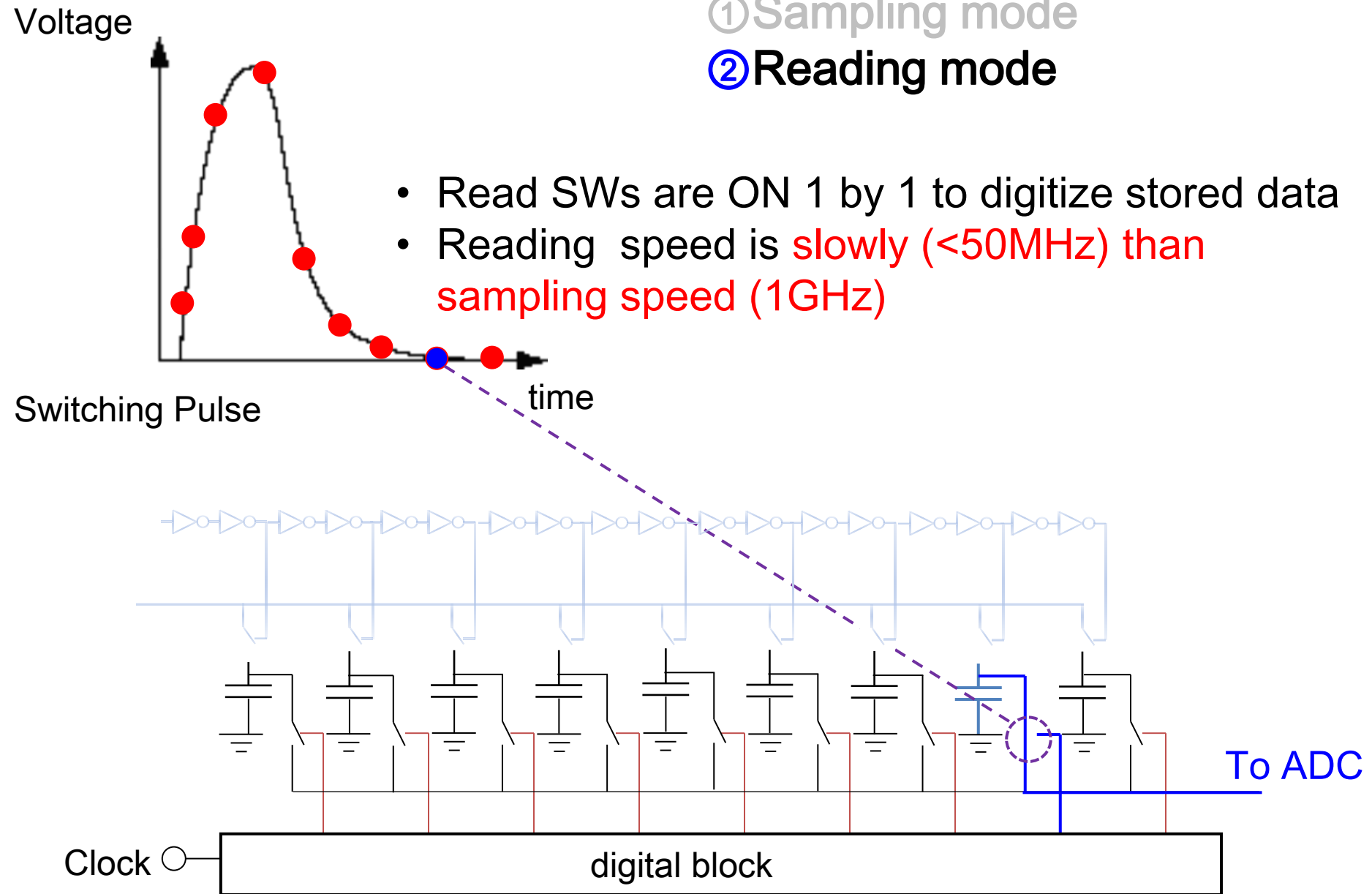


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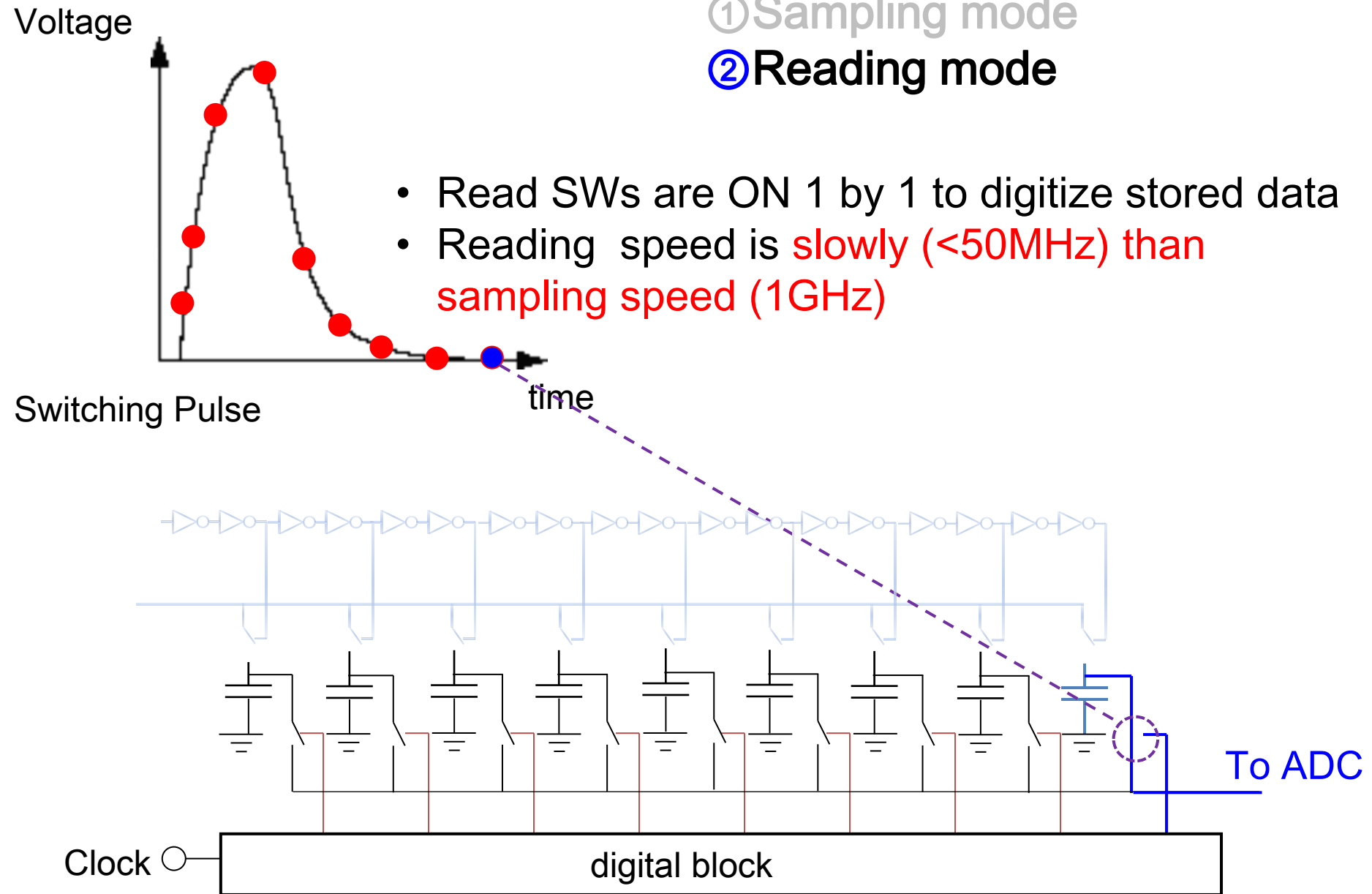


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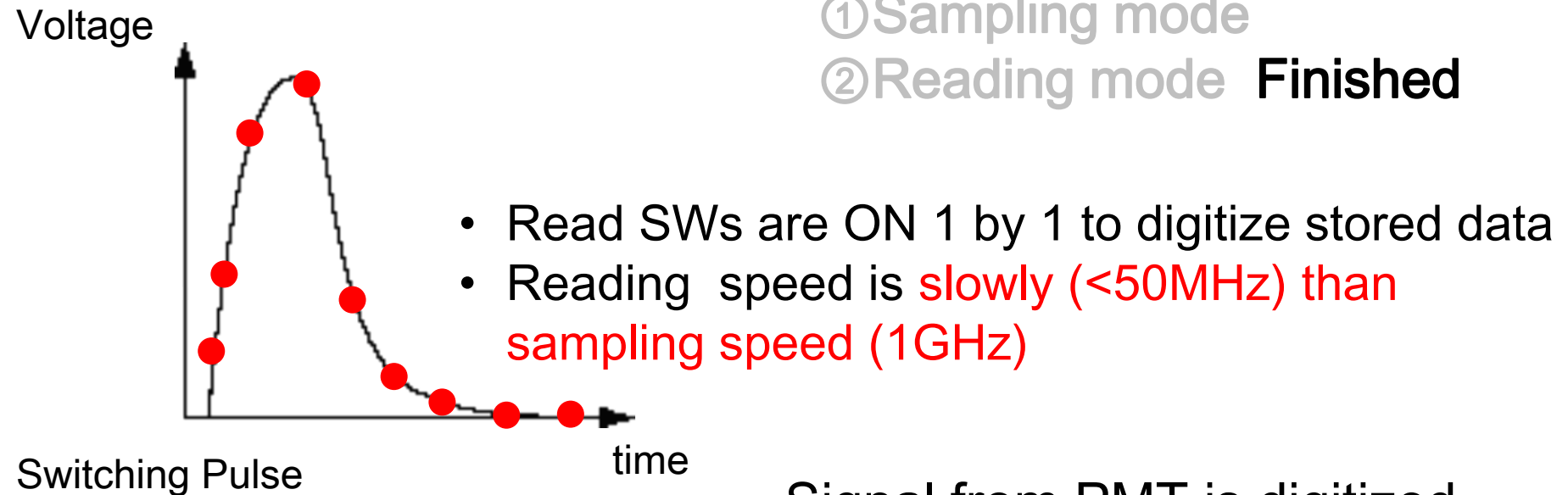
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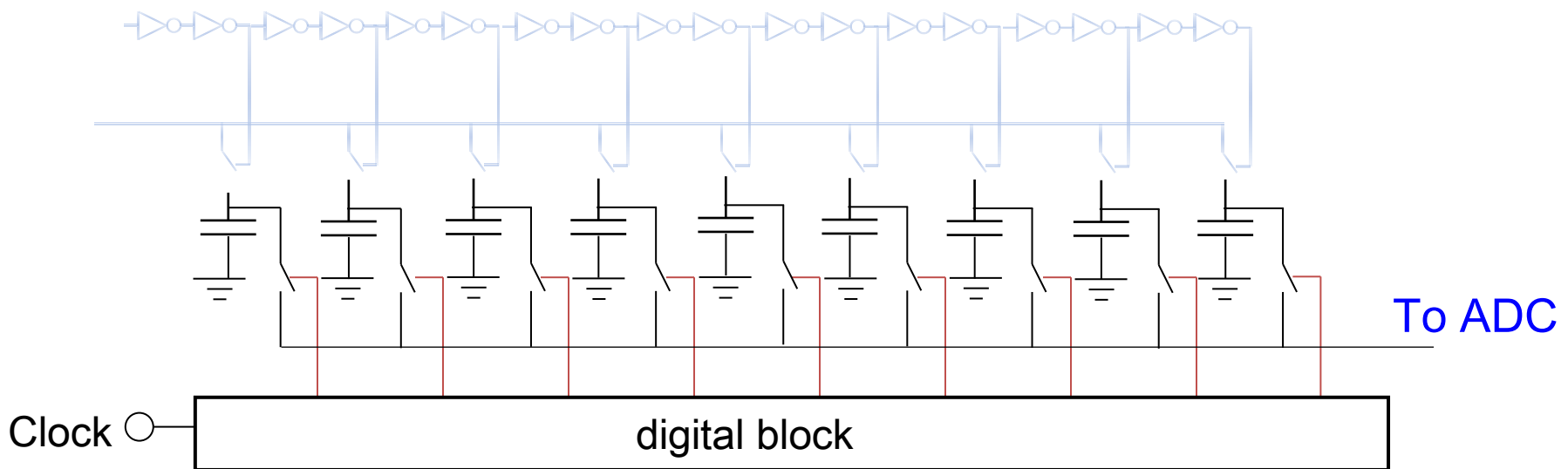
How AMC sample voltage

① Sampling mode

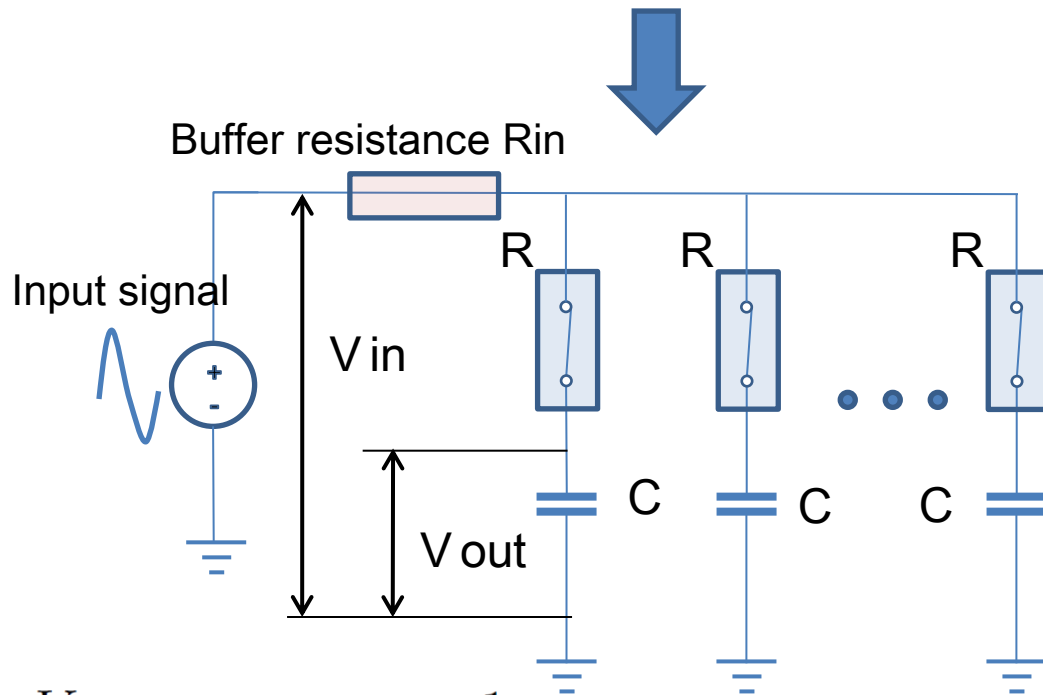
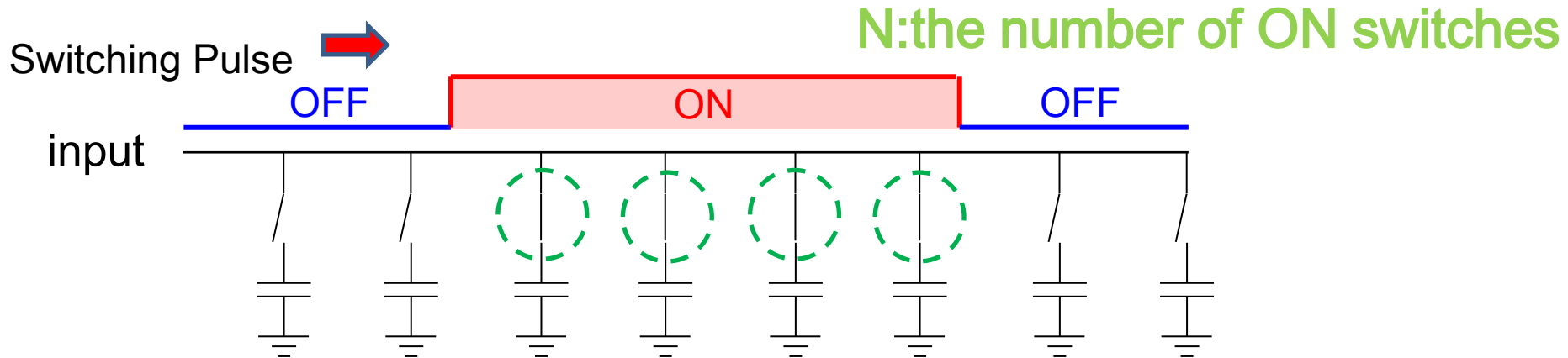
② Reading mode **Finished**



Signal from PMT is digitized



Design ~analog bandwidth~



Analog bandwidth : f (-3dB)

$$f = \frac{1}{2\pi(RC + NR_{in}C)}$$

R : SW ON resistance

C : capacitance

R_{in} : resistance of output buffer

N : the number of ON switches

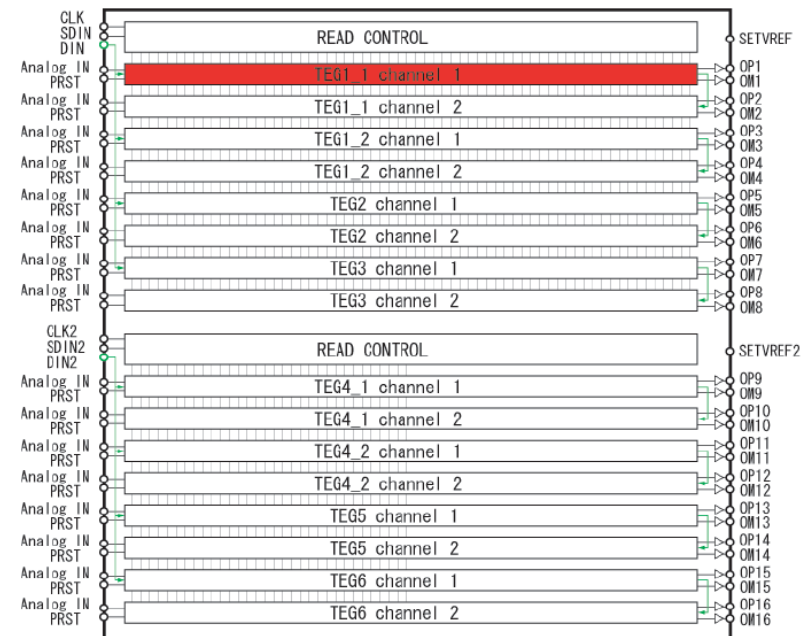
-keep low N to improve f

$$\frac{V_{out}}{V_{in}} = \frac{1}{1 + j\omega RC + j\omega NCR_{in}}$$

Test Element Group(TEG)

- We Fabricated 6 types Test Element Group as test pieces
- TEGs have different capacitor and architecture

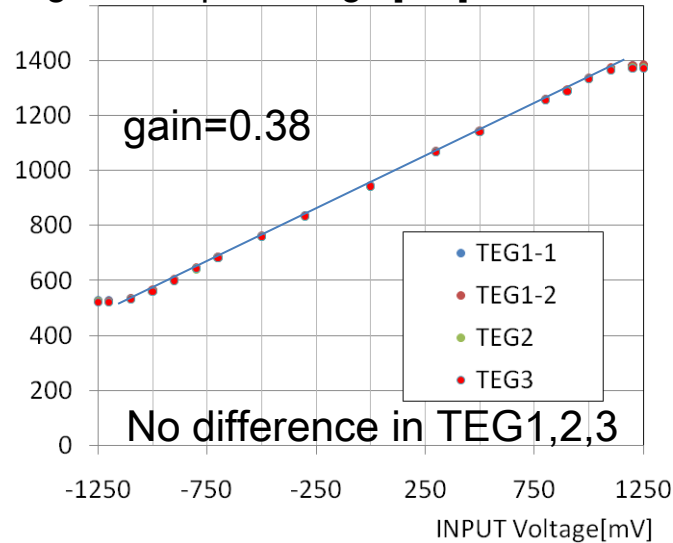
	capacitance	Architecture
TEG1	75fF	Typical
TEG2		Symmetry
TEG3		Simple
TEG4	400fF	Typical
TEG5		Symmetry
TEG6		Simple



Linearity

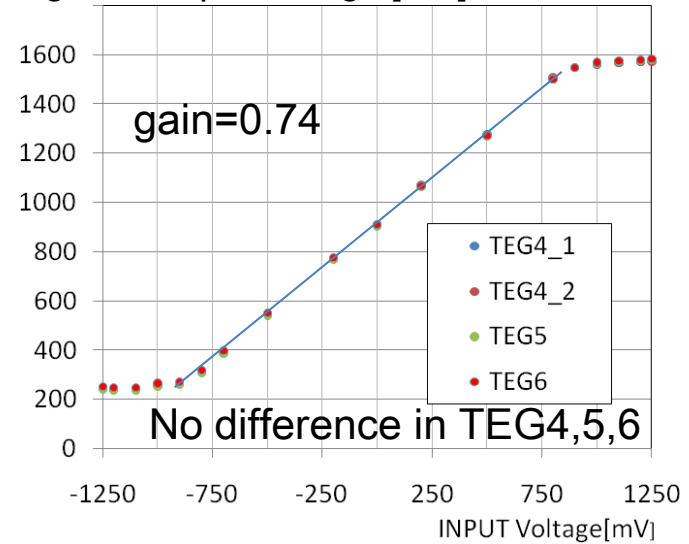
75fF TEG linearity

average of output voltage [mV]



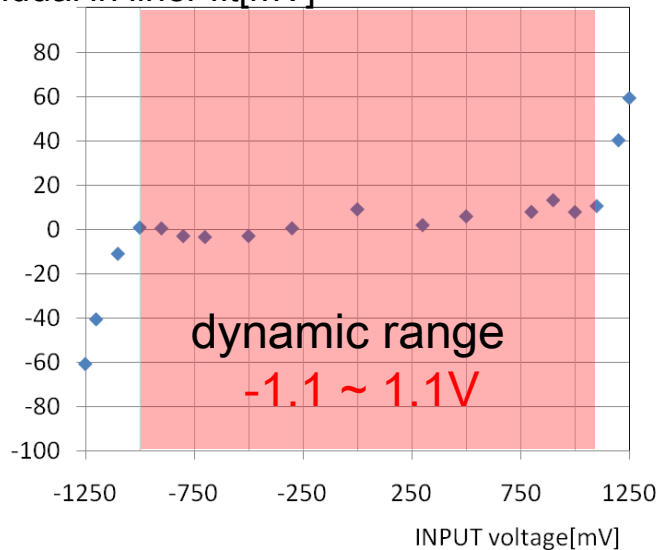
400fF TEG linearity

average of output voltage [mV]



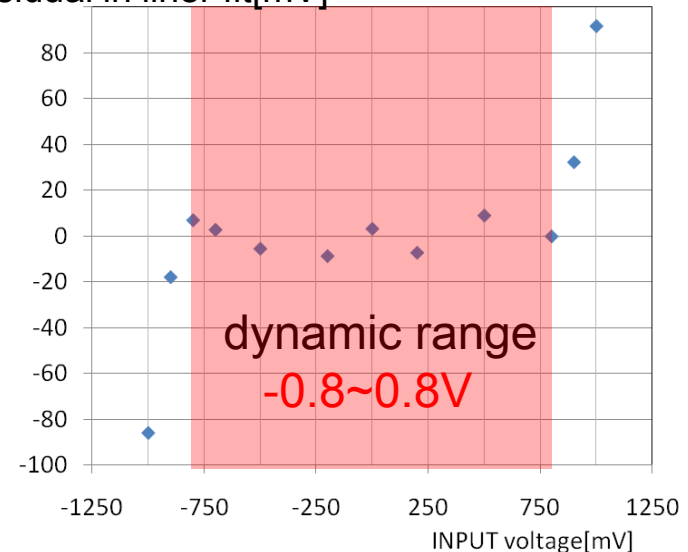
residual in liner fit for 75fF TEG

residual in liner fit[mV]



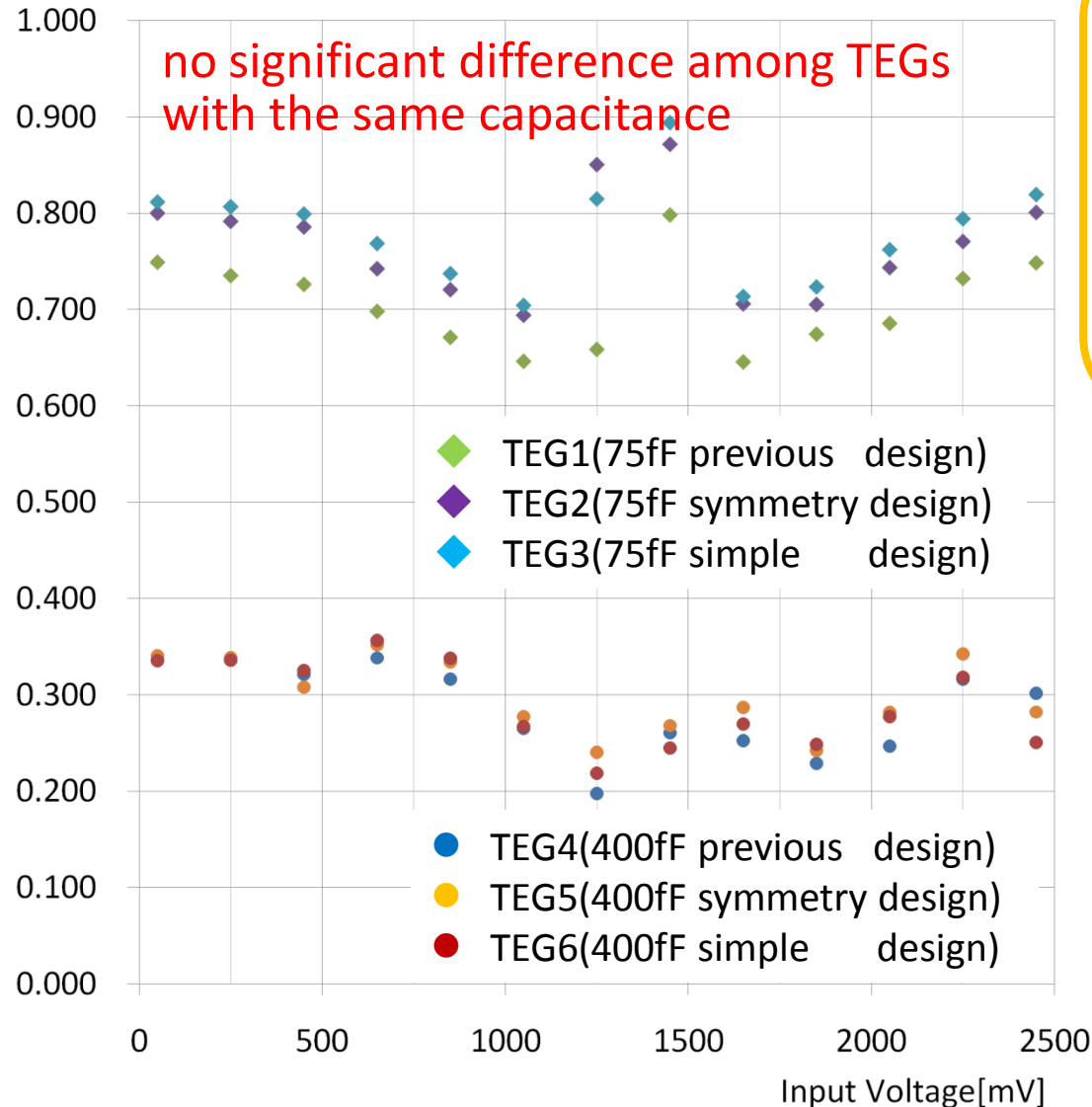
residual in liner fit 400fF TEG

residual in liner fit[mV]



Noise(RMS of measured voltages)

Noise standard deviation [mV]



X axis:
input voltage

Y axis:
standard deviation of output
voltages in 32 cells for
1000 events with the
constant input voltages

Typical noise voltages

$\sigma=0.8\text{mV}$ 75fF TEG1,2,3

$\sigma=0.4\text{mV}$ 400fF TEG4,5,6

resolution for 75fFTEGs

$2.2\text{V}/0.8\text{mV}\sim 10\text{bits}$

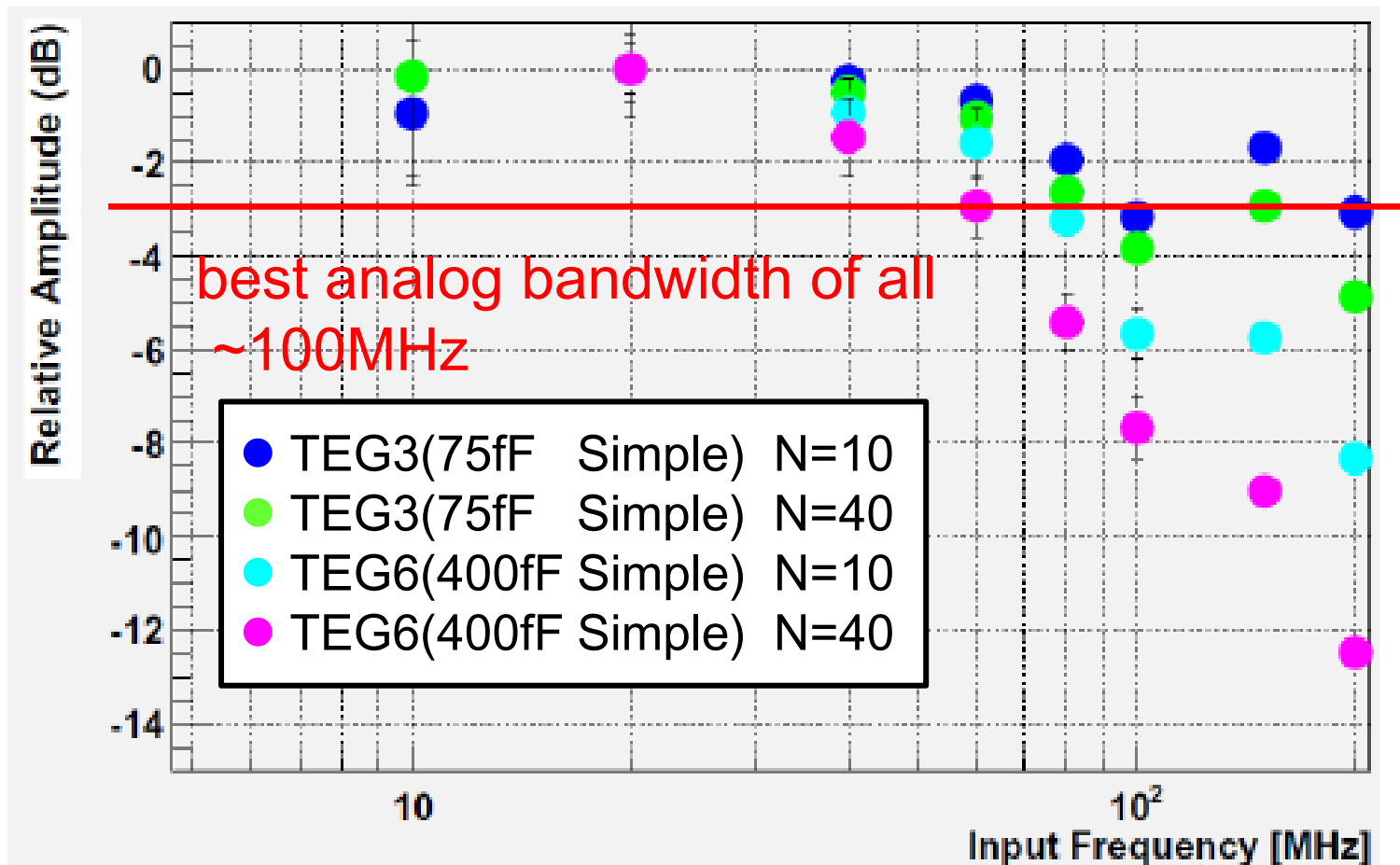
resolution for 400fFTEGs

$1.6\text{V}/0.4\text{mV}\sim 11\text{bits}$

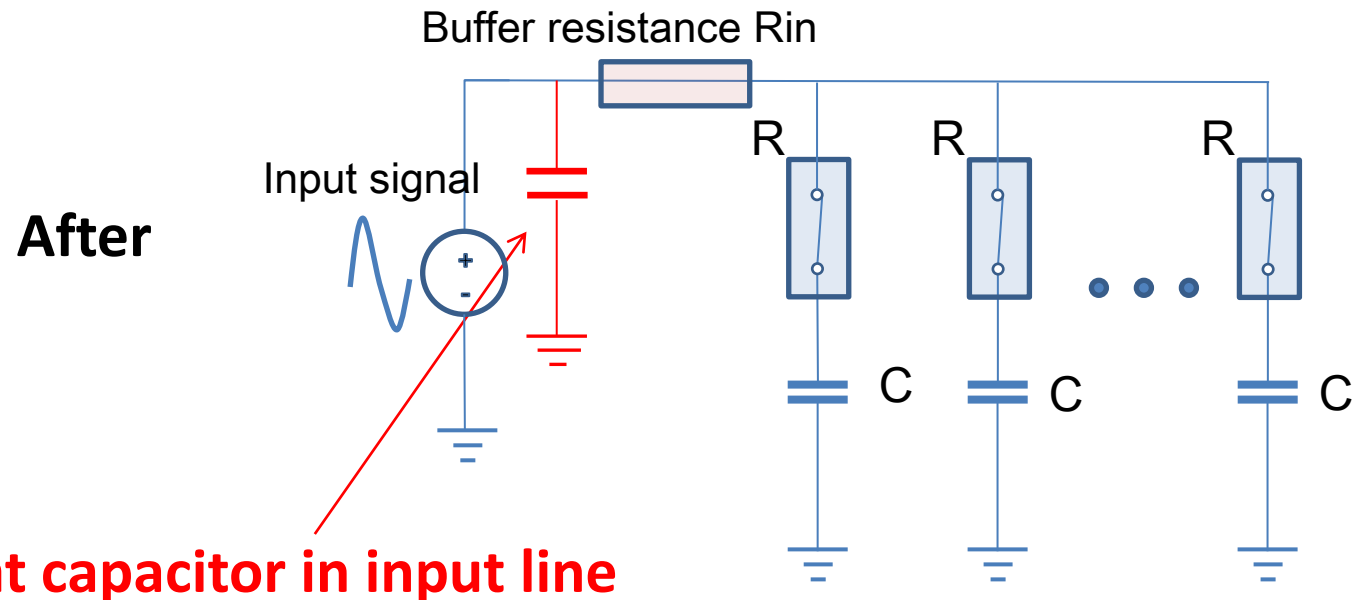
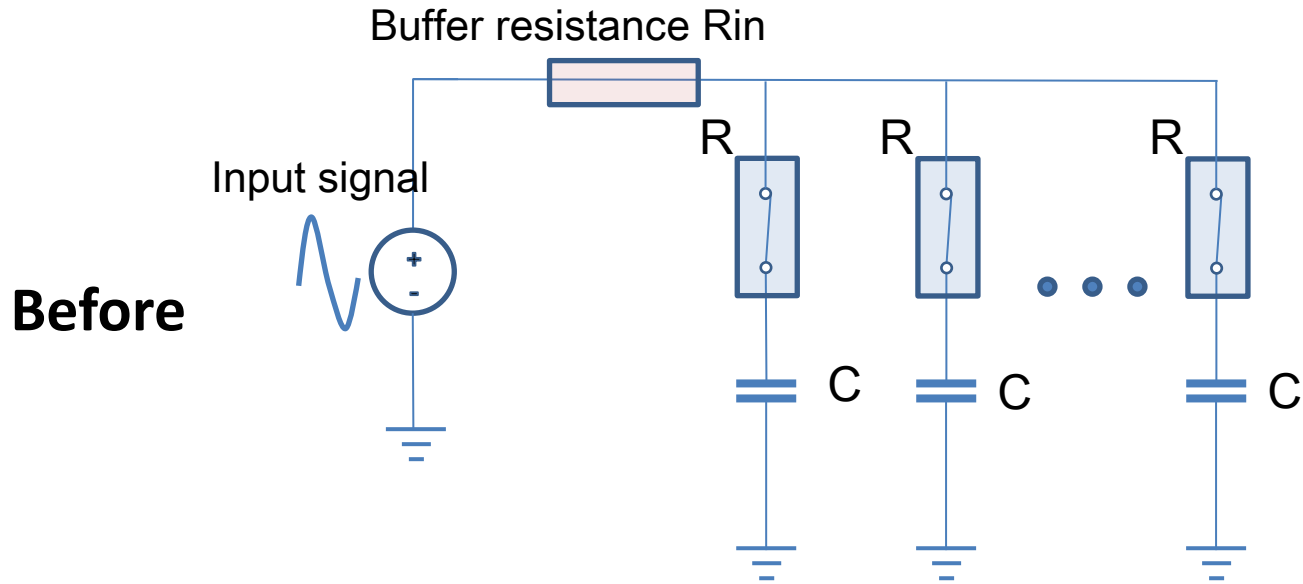
Achieve target 10bits!

Analog bandwidth

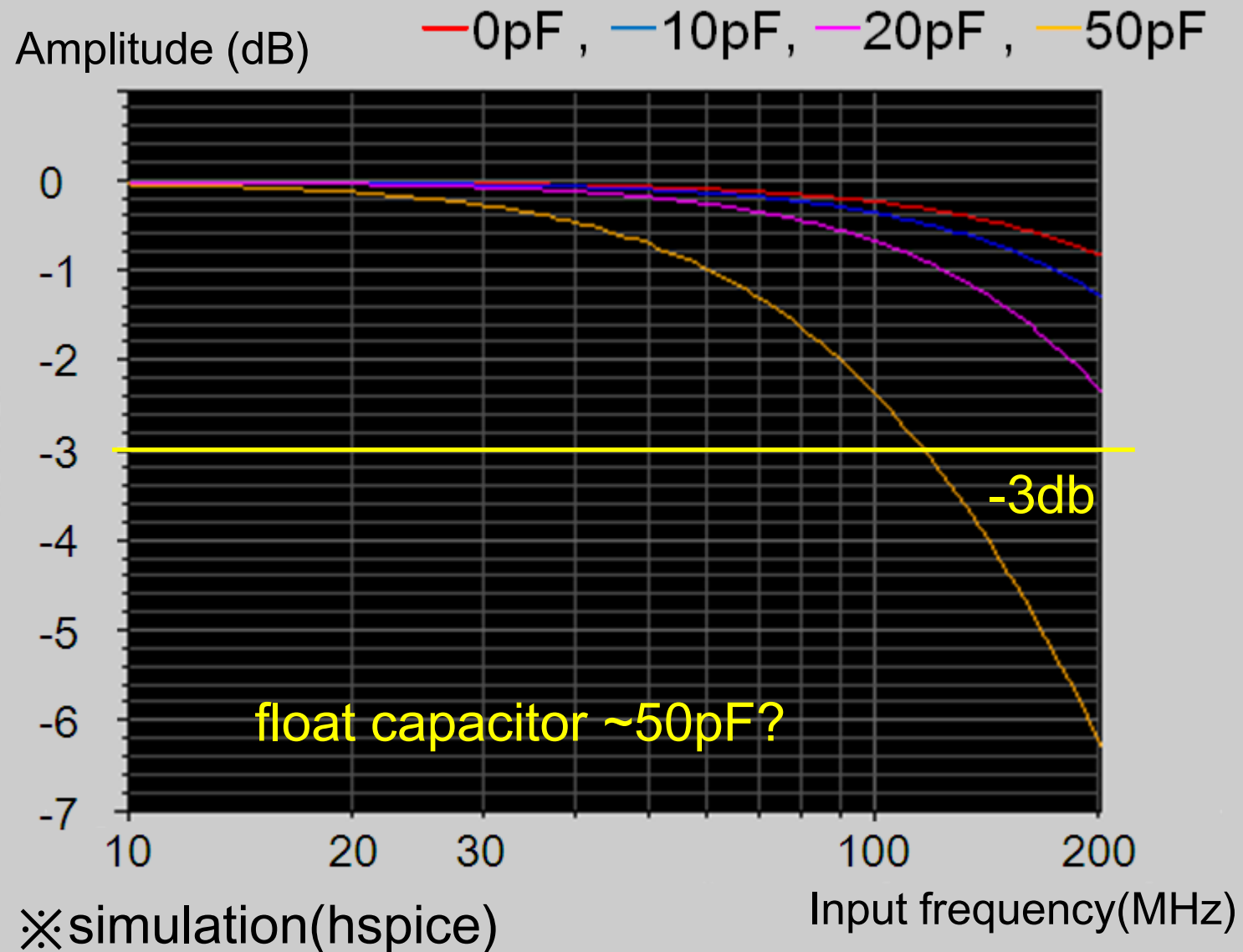
- TEG3 is the best among TEG1~3 ,TEG6 is the best among TEG4~6
 - Simple TEGs show the best analog bandwidth
- The better Analog bandwidth is shown in the operation with the smaller N
 - N is the number of ON switches



Simulation of analog bandwidth



Simulation result



Summary

- AMC contributes to lower threshold energy
- Good results except for analog bandwidth
- Analog bandwidth of 100MHz should be improved
 - extra capacitance and resistance limit analog bandwidth
 - The smaller N gives a better analog bandwidth
- Simple Designs like TEG3 and 6 make analog bandwidth higher

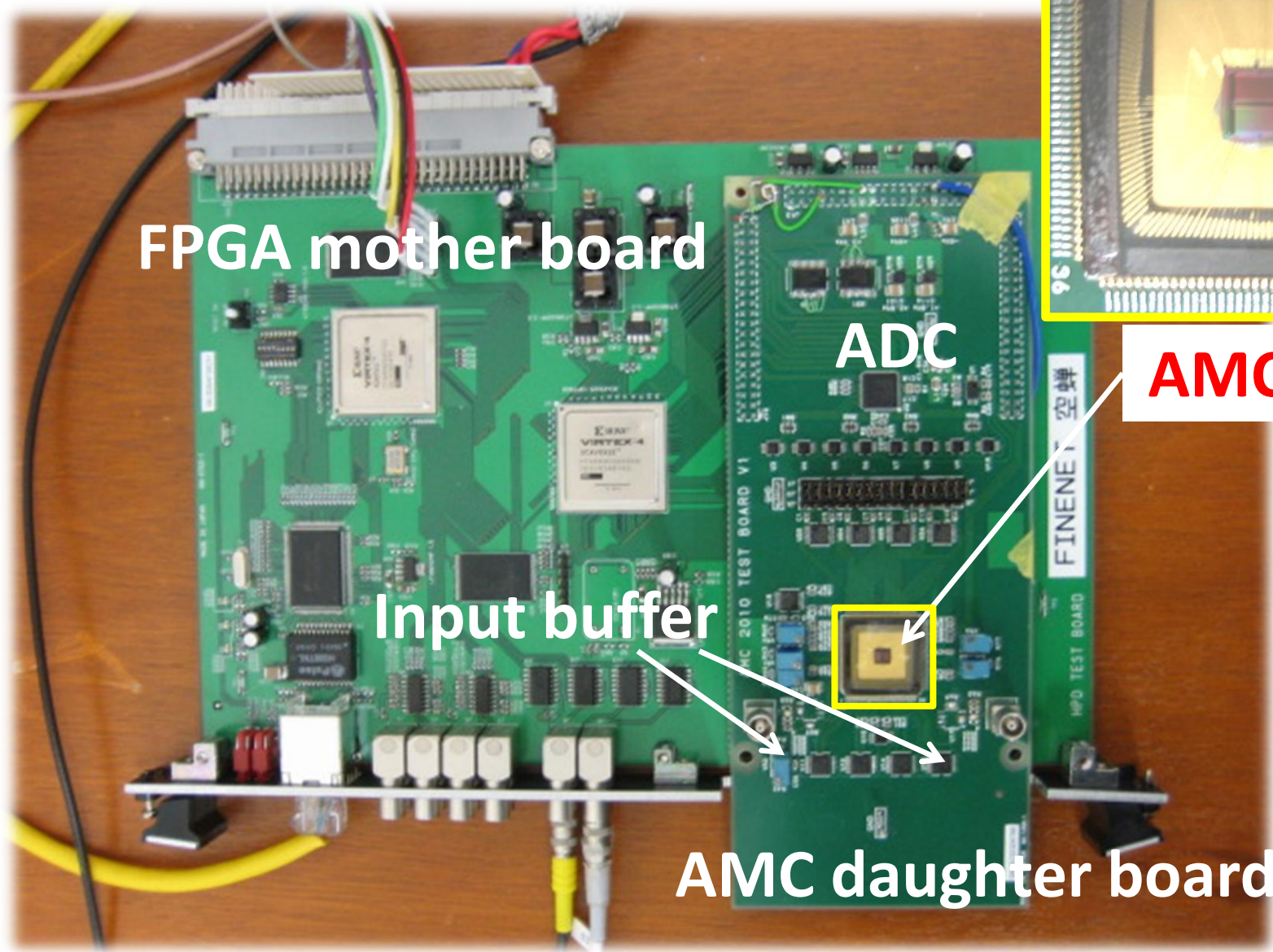
Future plans

- I would like to contribute to design study of CTA and the upgrade of MAGIC, especially to the readout electronics with my experience
- I am also motivated to challenge new hardware developments: advanced photo detector SiPM etc
- This development contribute to achieve better sensitivity in low energy especially to study extra galactic sources and fundamental physics

Thank you for your attention

Back up

Test setup

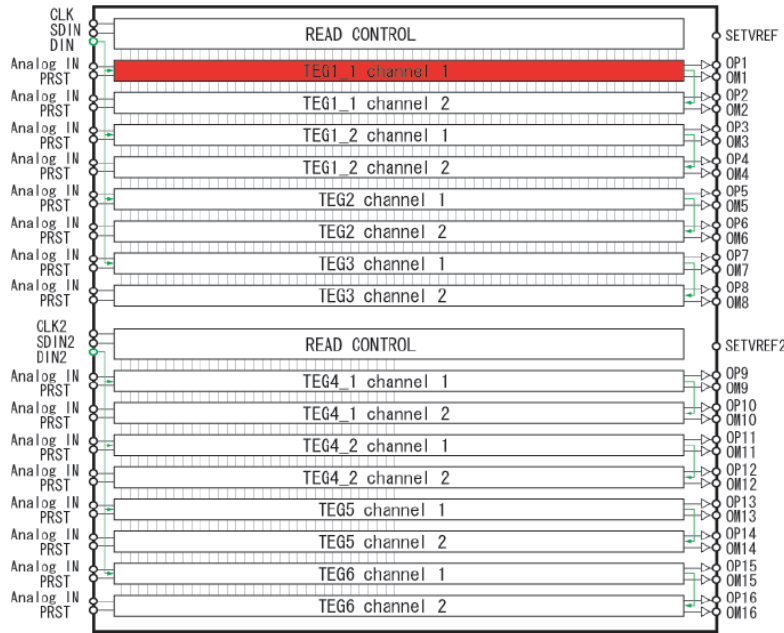


Results

		TEG1	TEG2	TEG3	TEG4	TEG5	TEG6
Cell capacitance (fF)		75	75	75	400	400	400
Offset canceling SW		CMOS	CMOS	NMOS	CMOS	CMOS	NMOS
SW formation		Common	1 by 1	1 by 1	Common	1 by 1	1 by 1
Architecture NOTE:		typical	symmetry	simple	typical	symmetry	simple
Switch speed(GHz)		~1	~1	~1	~1	~1	~1
Dynamic range(V)		2.2	2.2	2.2	1.6	1.6	1.6
Linearity(maximum residual) (mV)		15	15	15	10	10	10
Gain		0.38	0.38	0.38	0.74	0.74	0.74
Average of noise(mV)		0.76	0.82	0.84	0.42	0.41	0.42
resolution(bit)		10.1	10.0	10.0	11.4	11.4	11.4
Analog bandwidth (MHz)	N=10	<100	<100	~100	<80	<80	80

red : clear target spec blue: NOT clear target spec

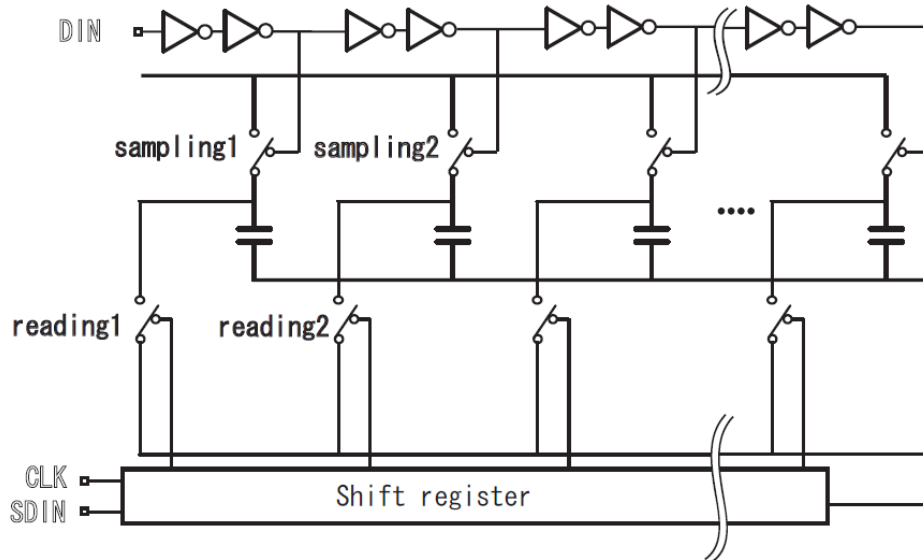
Test Element Group(TEG)



- Fabricated 6 type test element group
 - different capacitor & architecture
- Add to differential system
 - have a clone TEG
 - take a difference between two TEGs
 - One has a signal with pedestal
 - The other has a just pedestal for canceling out common noise & offset in chip

	capacitance	Sample SW	Offset canceling SW	Offset canceling SW formation	Cell	Architecture
TEG1	75fF	CMOS	CMOS	Common	128	Typical
TEG2				1 by 1		Symmetry
TEG3			NMOS	Simple		
TEG4	400fF		CMOS	Common	64	Typocal
TEG5				1 by 1		Symmetry
TEG6			NMOS	Simple		

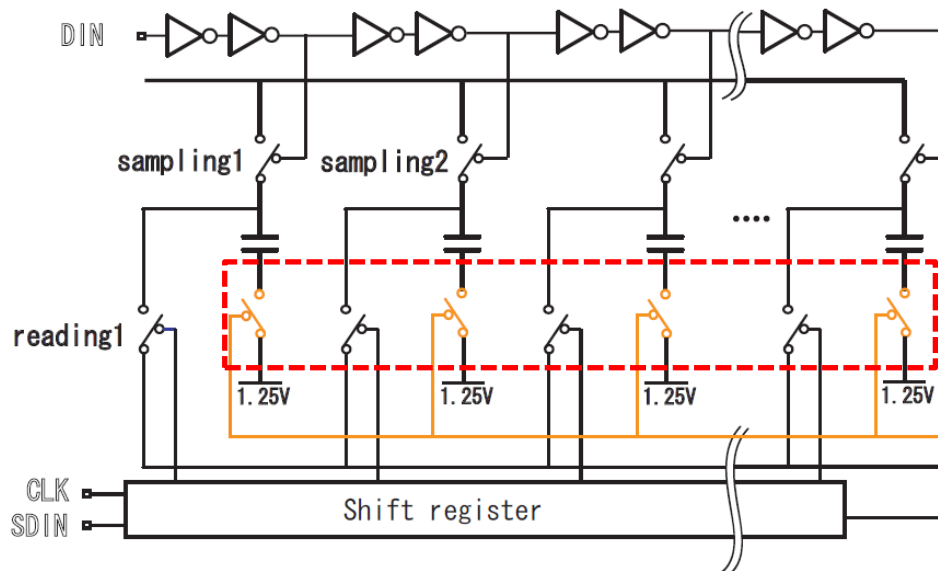
Offset canceling SW formation



Offset canceling SW formation

COMMON

This is called as typical.



Offset canceling SW formation

1 by 1 (individual)

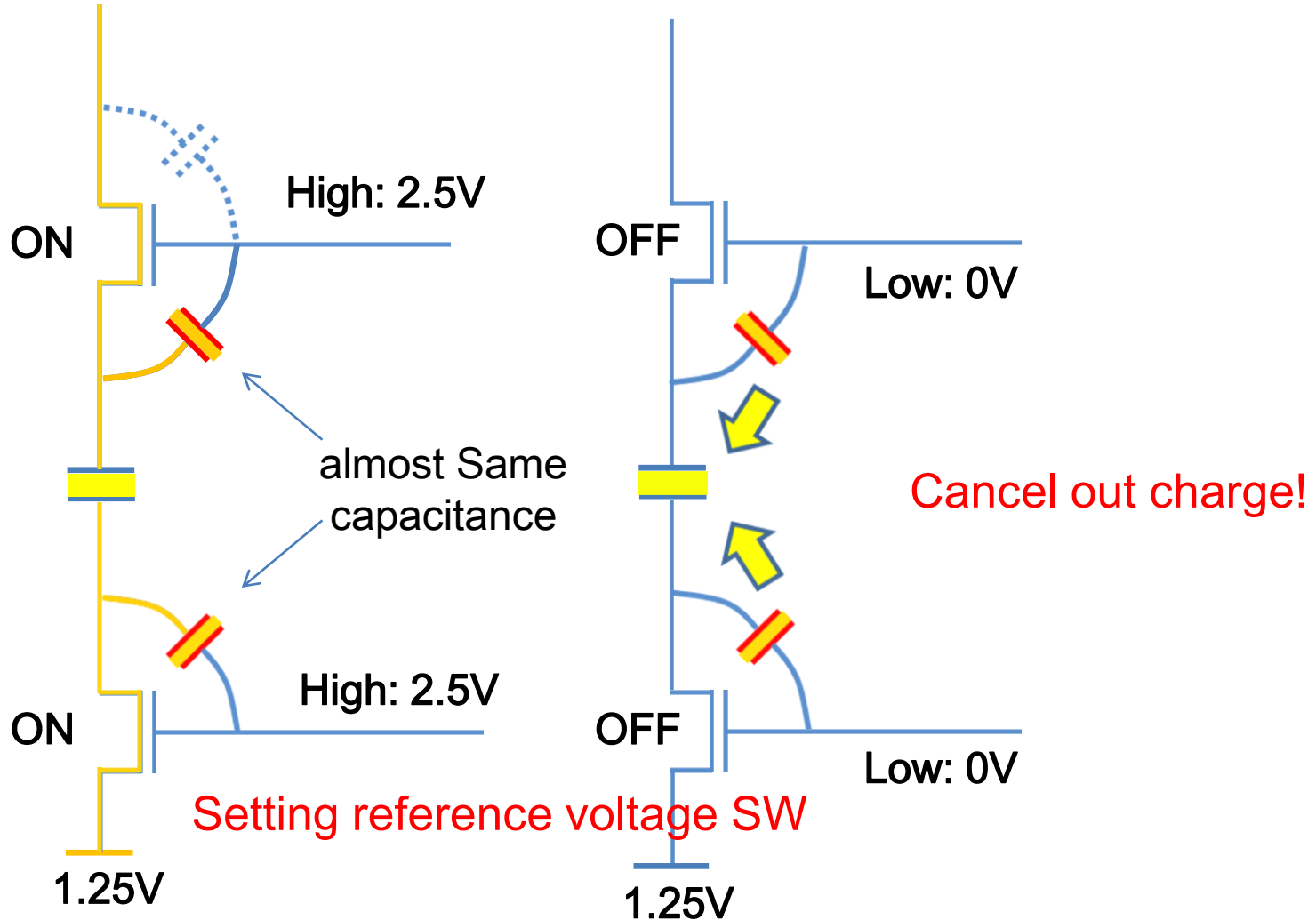
CMOS switch type (symmetric)

NMOS switch type (simple)

Design ~Offset canceling~

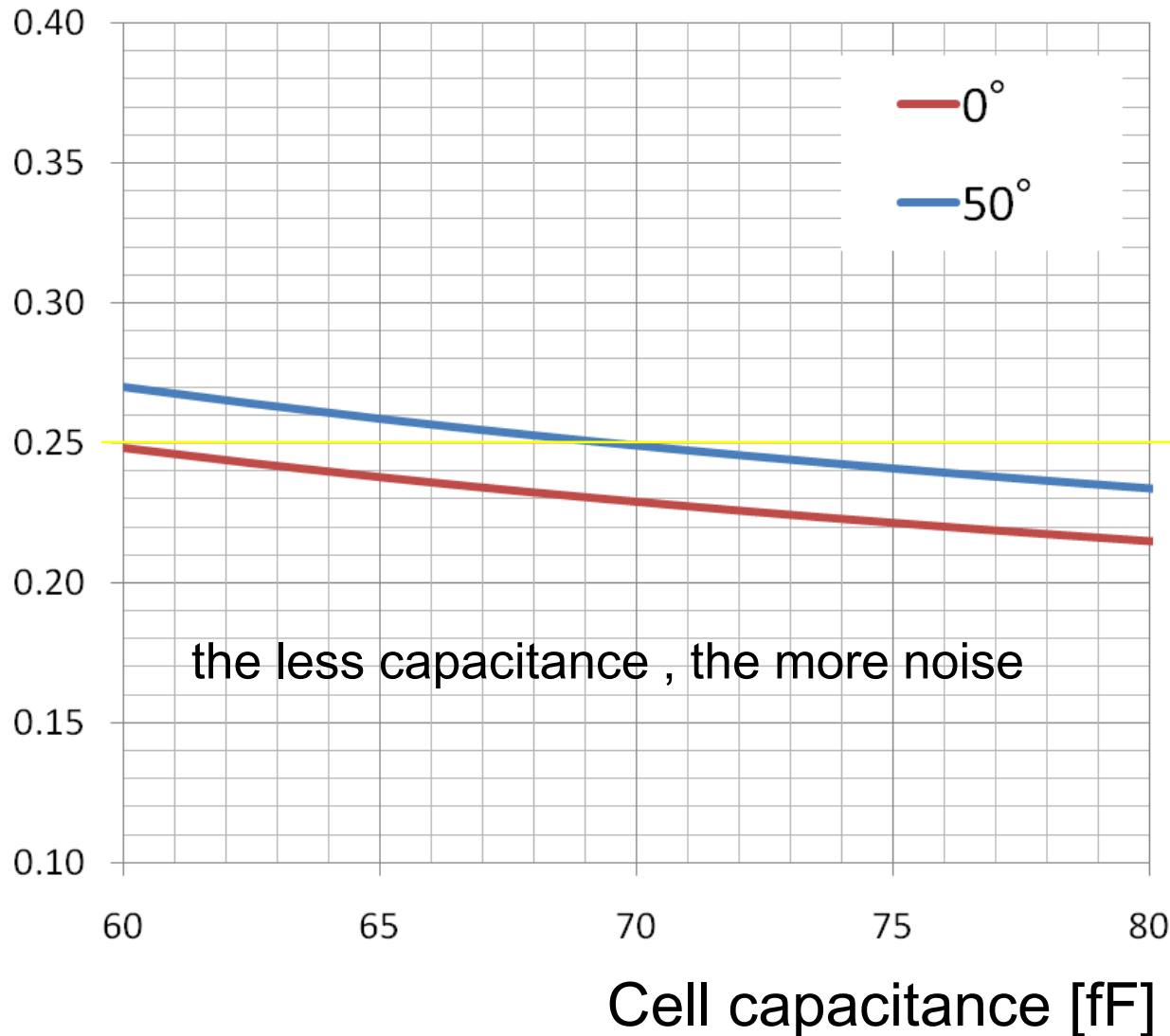
input

Sample SW is CMOS but simplify NMOS now



Design ~Thermal noise~

Noise voltage V_{rms} [mV]



$$V_{rms} = \sqrt{\frac{kT}{C}}$$

k: boltzmann constant
C: capacitor
T: temparture

target voltage

V_{rms} : 0.25mV

we safely setting
(dynamic range 1V
& 12bits)

$1/2^{12} \times 1V = 0.25mV$

select 75fF

Switching speed

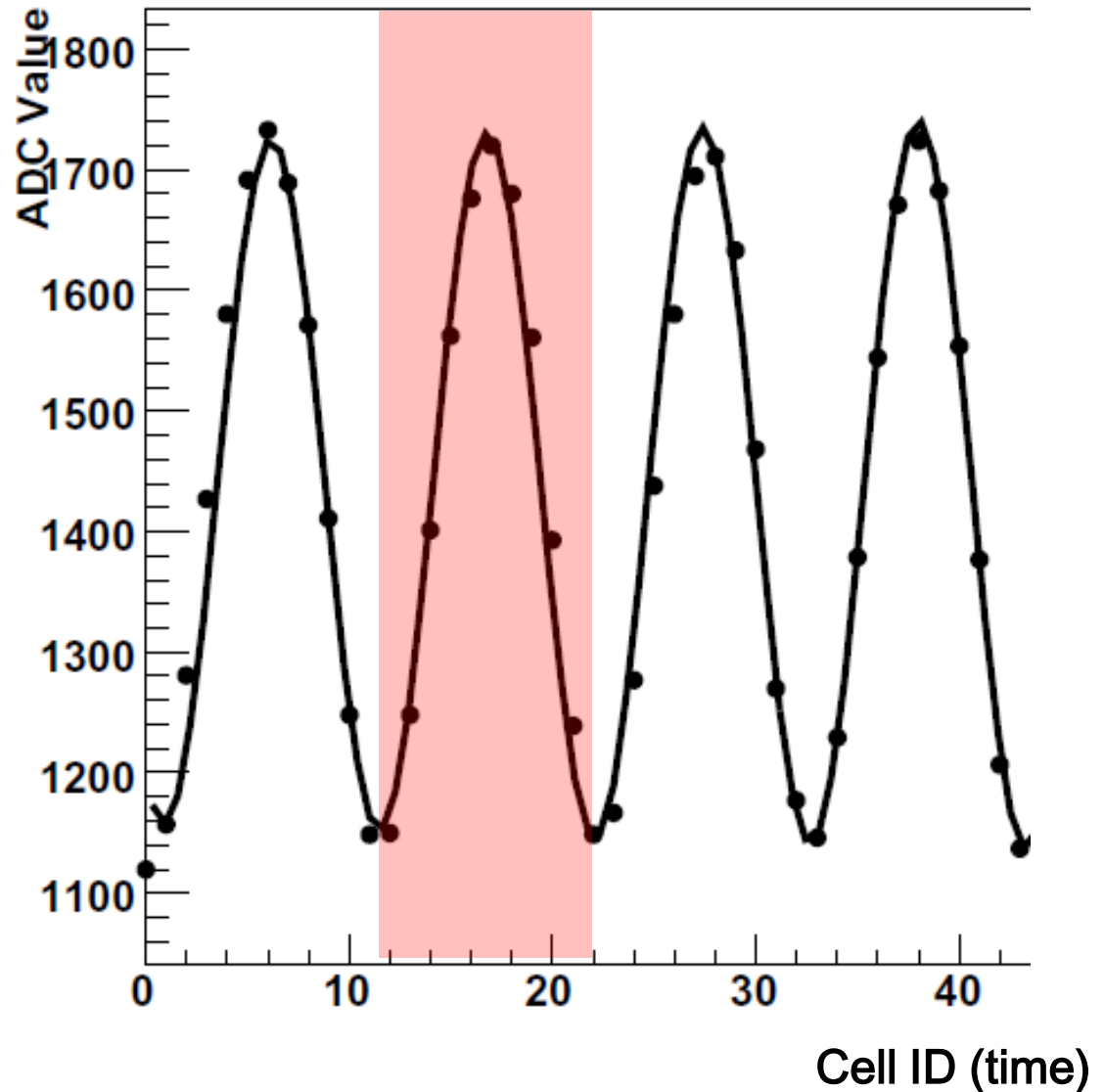
Y axis : ADC count
X axis : Cell ID

Input: 100MHz
sinusoidal wave
(period 10nsec)

The number of data
points in 1 cycle
about 10

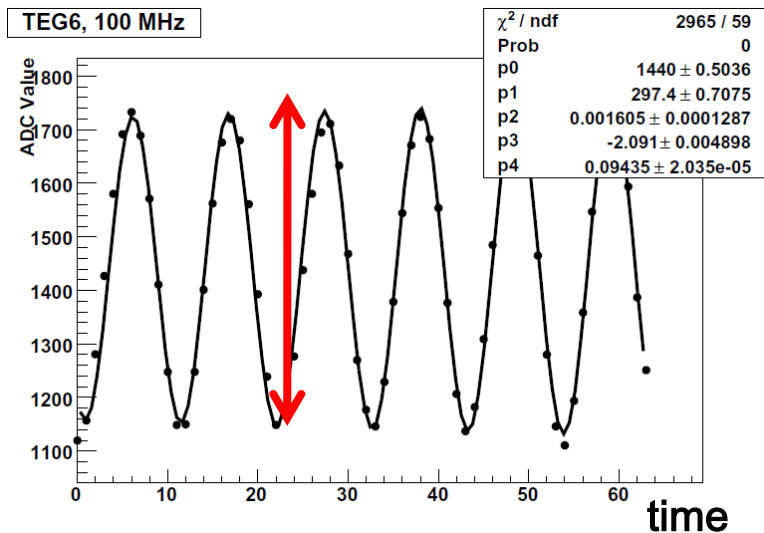
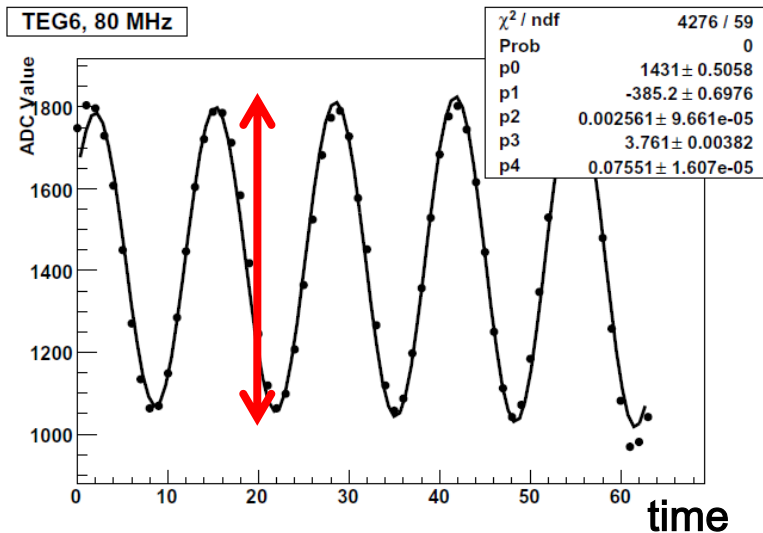
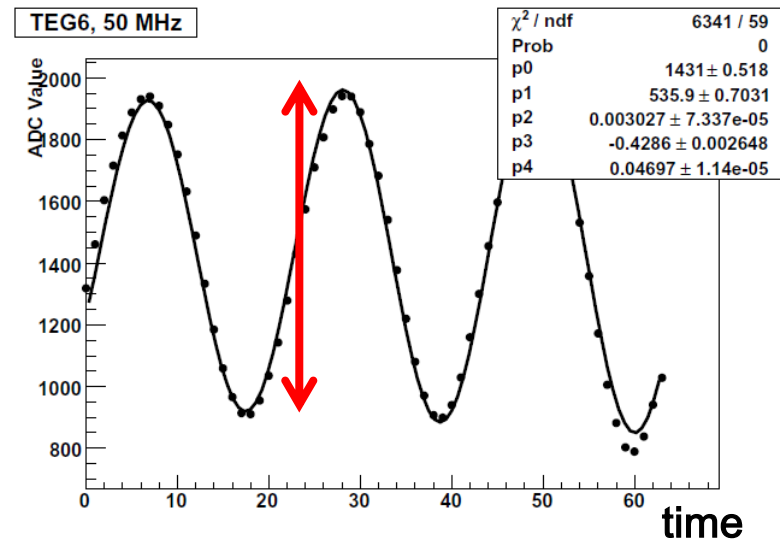
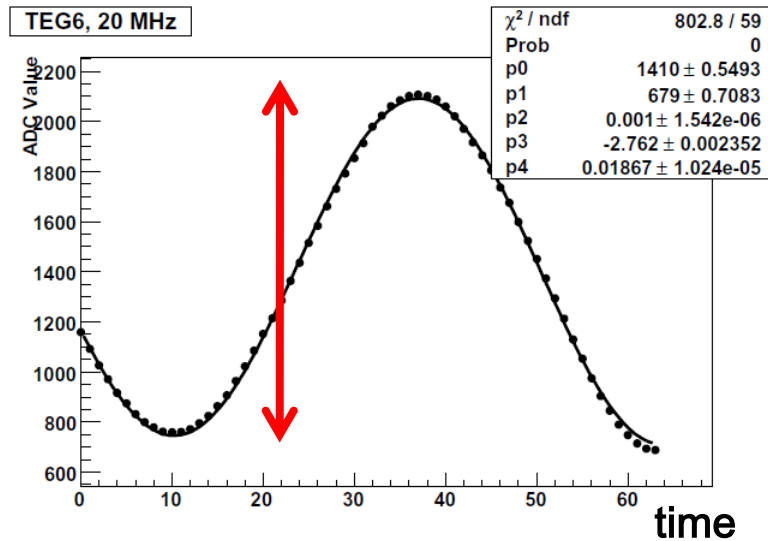


Switching speed
~1GHz



Analysis method analog bandwidth

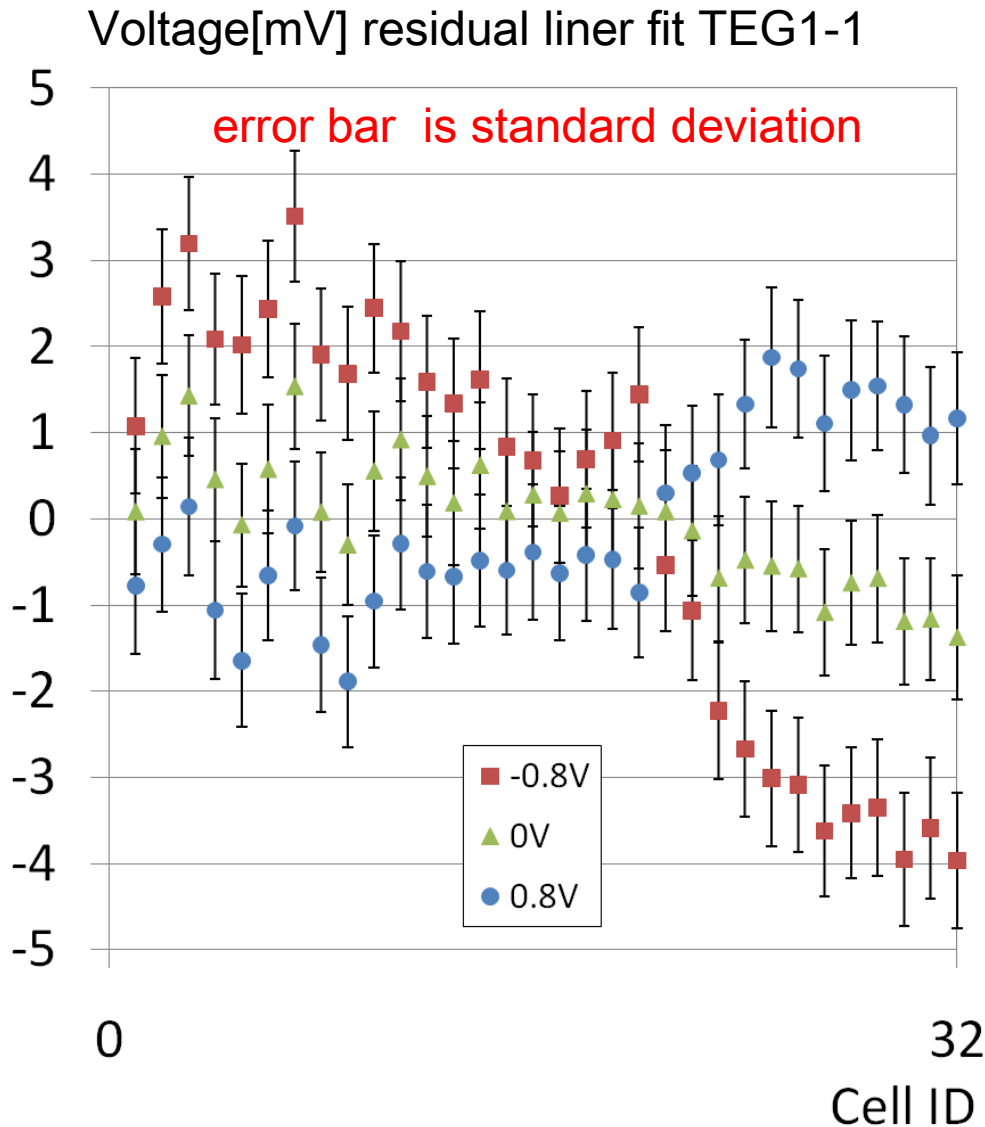
1. Input various frequency wave
2. fitting wave
3. estimate **amplitude**



Discussion residual in liner fit

Vertical axis: residual liner fit cell by cell

Horizontal axis: cell ID



different by in put voltage & cell



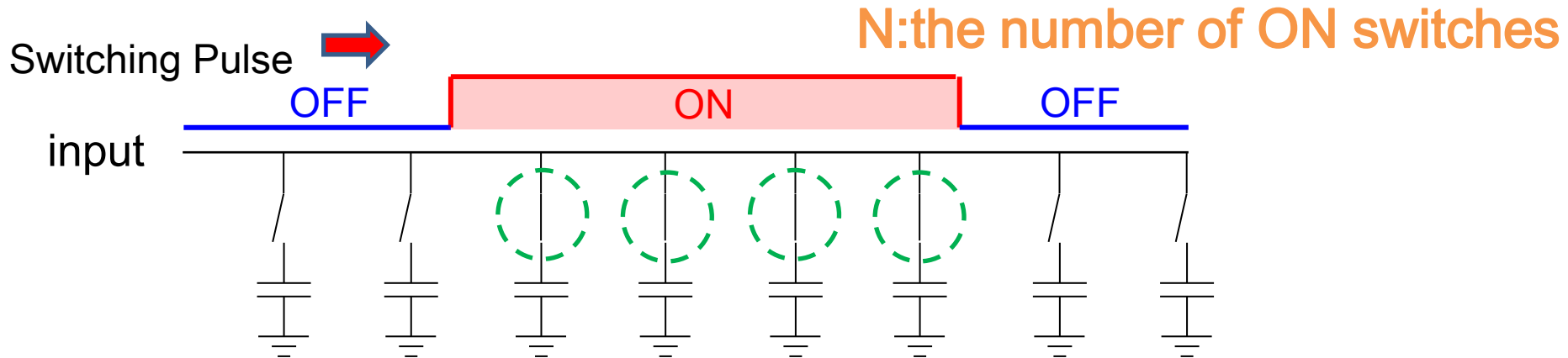
but error bar is
not almost different!



We need to know residual by
cell & input voltage

Temperature depends on residual?
(will check when I come back Japan)

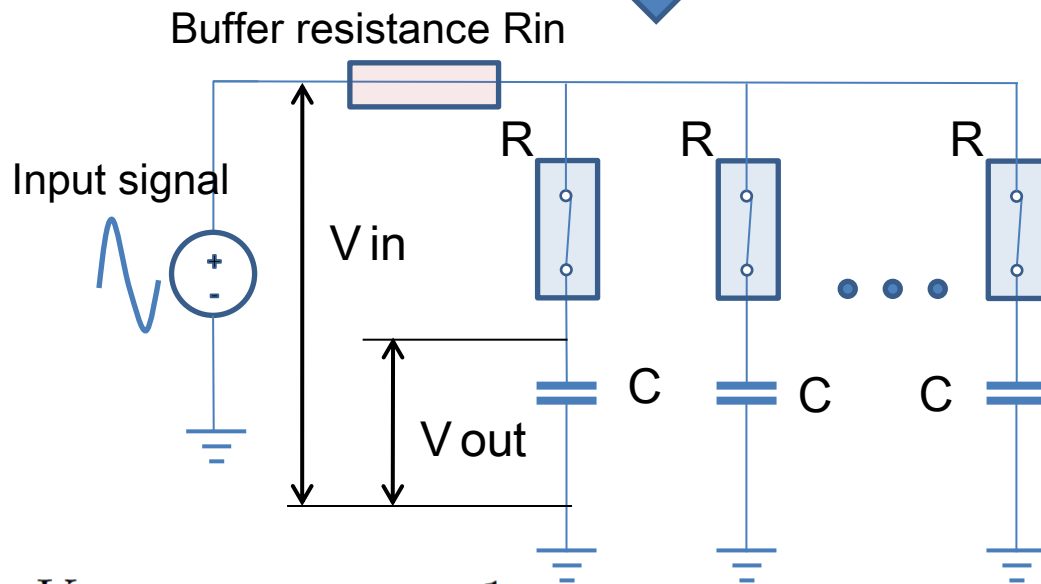
Design ~analog bandwidth~



N: the number of ON switches

Analog bandwidth : f (-3dB)

$$f = \frac{1}{2\pi(RC + NR_{in}C)}$$



R : SW ON resistance
~2000 Ω

C : capacitance
60~1000fF

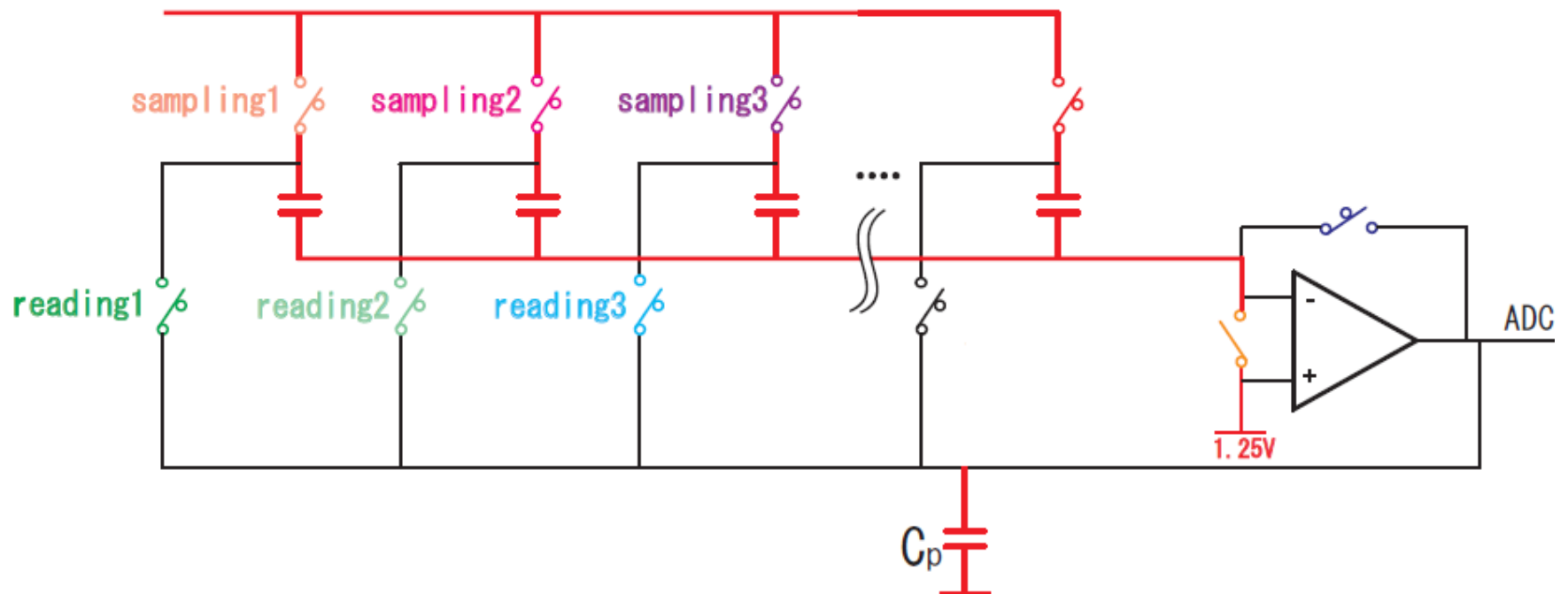
R_{in} : resistance of output buffer
~200 Ω

N : the number of ON switches

-keep low N to improve f

$$\frac{V_{out}}{V_{in}} = \frac{1}{1 + j\omega RC + j\omega NCR_{in}}$$

Difference of gain



AMC Power consumption

	Power consumption (mW)
AMC+AMC test board +FPGA(reading board)	10400
FPGA(reading board)	7490
AMC+AMC test board	2910

※AMC test board including input buffers(*8) & ADC power consumption

Target specification

AMC processed by $0.25\mu\text{m}$ technology

- charge resolution (10 bits)
- Sampling speed (1 GHz)
- Analog bandwidth (300 MHz)
 - enough to record original shapes of Cherenkov light signals

We can estimate light of shower correctly

